



US009151807B2

(12) **United States Patent**
Friedrich et al.

(10) **Patent No.:** **US 9,151,807 B2**
(45) **Date of Patent:** ***Oct. 6, 2015**

- (54) **CIRCUITS AND METHODS FOR GENERATING A SELF-TEST OF A MAGNETIC FIELD SENSOR**
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- (*) Notice: Subject to any disclaimer, the term of this patent is extended or adjusted under 35 U.S.C. 154(b) by 0 days.
- This patent is subject to a terminal disclaimer.

- (52) **U.S. Cl.**
CPC **G01R 33/0035** (2013.01); **G01R 33/0023** (2013.01); **G01R 35/005** (2013.01)
- (58) **Field of Classification Search**
CPC **G01R 33/0023**; **G01R 33/0035**; **G01R 35/005**
See application file for complete search history.

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- (21) Appl. No.: **14/321,347**
- (22) Filed: **Jul. 1, 2014**
- (65) **Prior Publication Data**
US 2014/0312883 A1 Oct. 23, 2014

Related U.S. Application Data

- (63) Continuation of application No. 13/743,451, filed on Jan. 17, 2013, now Pat. No. 8,818,749, which is a continuation of application No. 12/706,318, filed on Feb. 16, 2010, now Pat. No. 8,447,556.
- (60) Provisional application No. 61/153,059, filed on Feb. 17, 2009.
- (51) **Int. Cl.**
G01R 27/28 (2006.01)
G01R 33/00 (2006.01)
G01R 35/00 (2006.01)

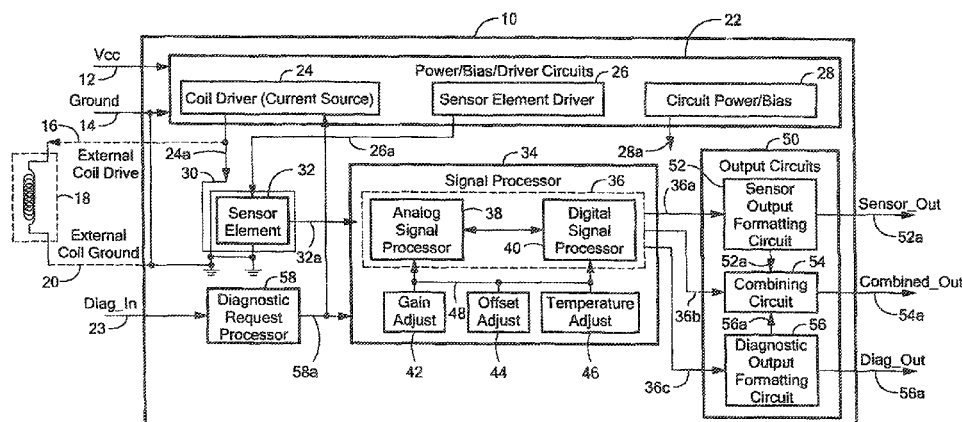
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(57) **ABSTRACT**

A magnetic field sensor includes built in self-test circuits that allow a self-test of most of, or all of, the circuitry of the magnetic field sensor, including self-test of a magnetic field sensing element used within the magnetic field sensor, while the magnetic field sensor is functioning in normal operation.

24 Claims, 24 Drawing Sheets



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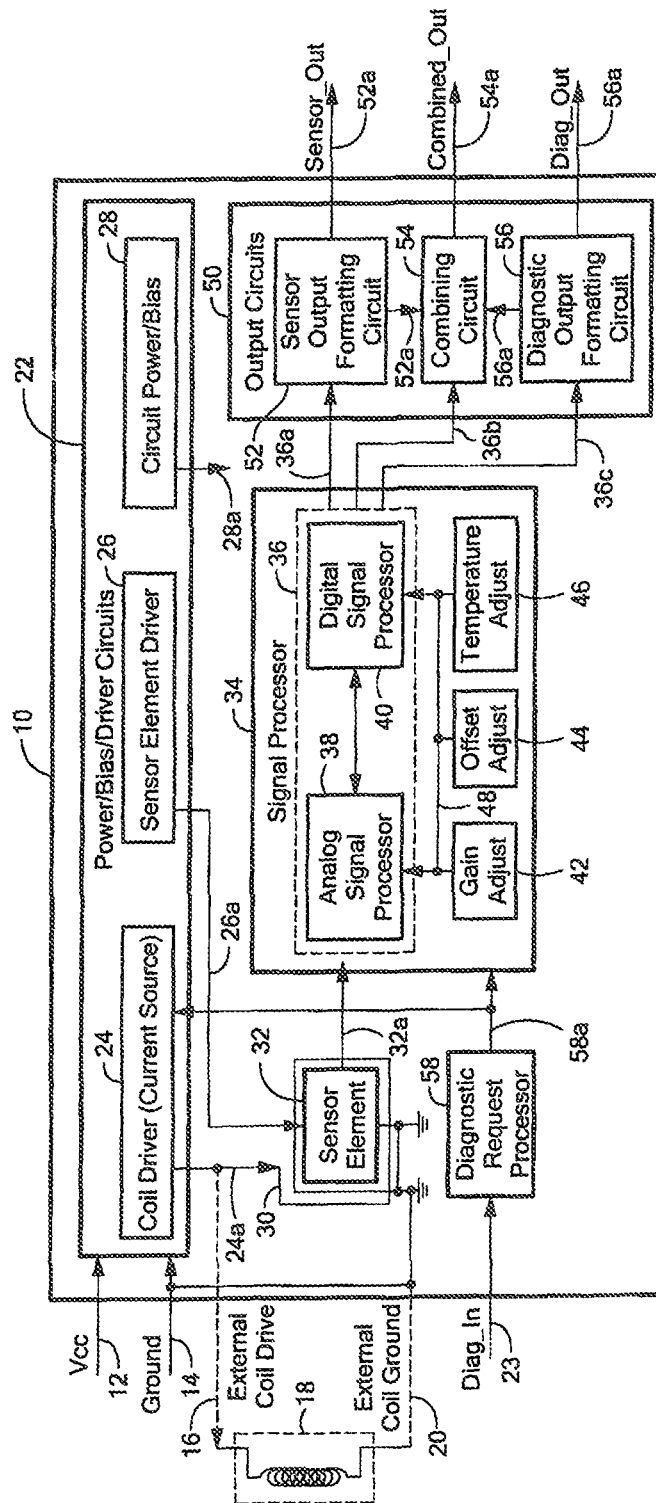


FIG. 1

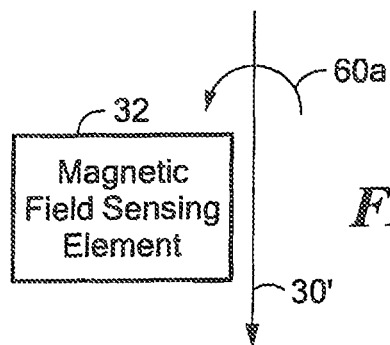


FIG. 2

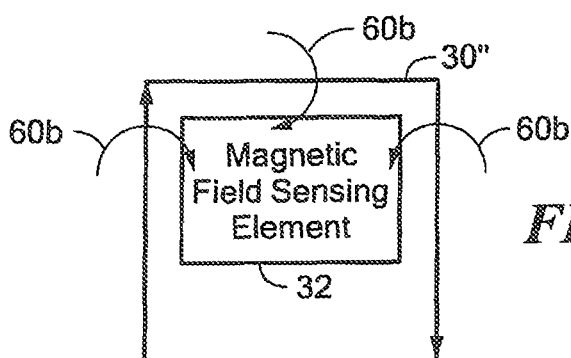


FIG. 2A

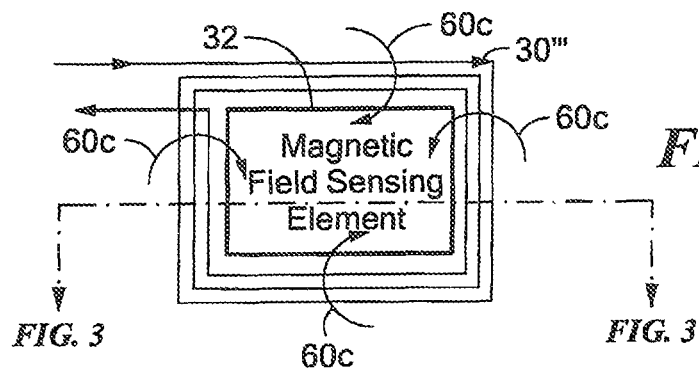


FIG. 2B

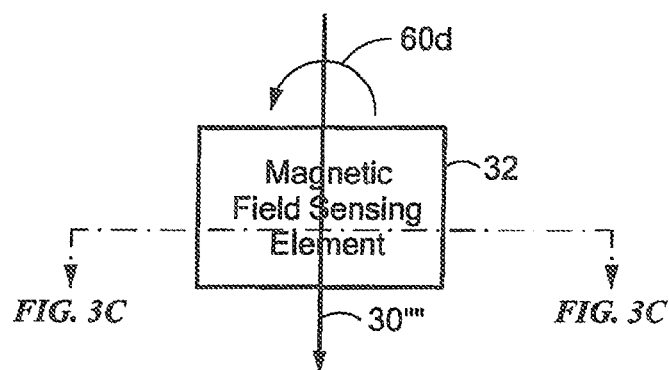


FIG. 2C

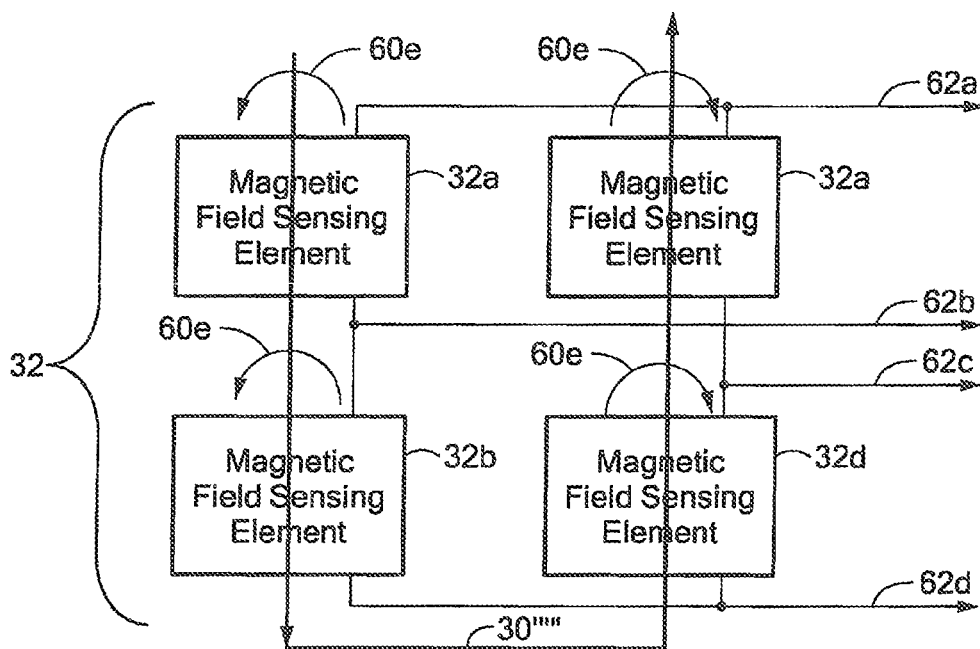


FIG. 2D

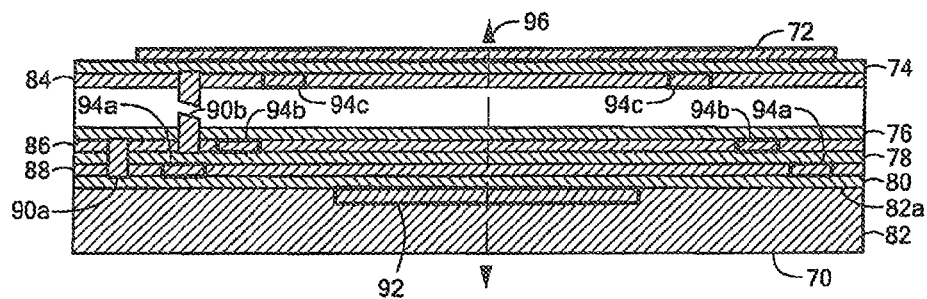


FIG. 3

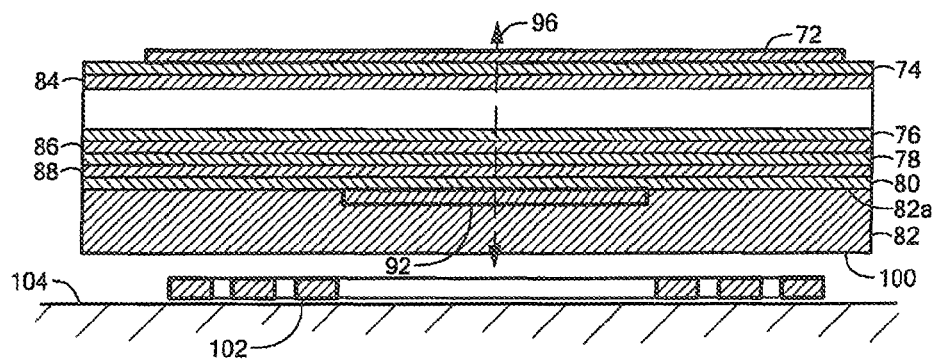


FIG. 3A

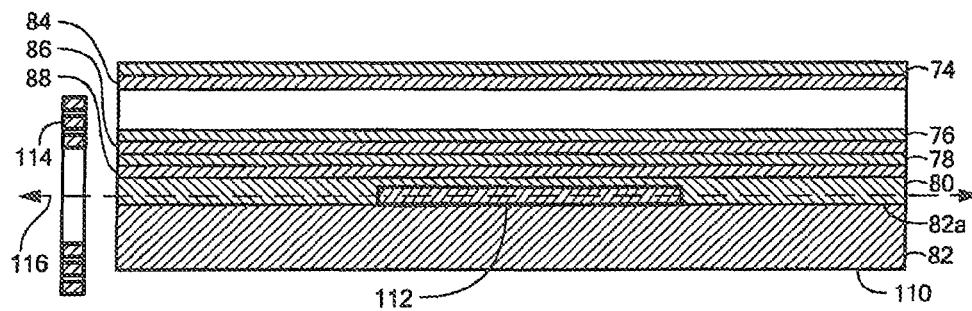


FIG. 3B

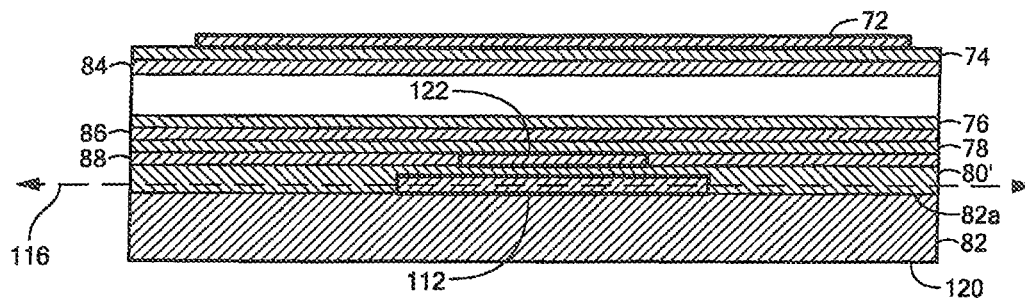


FIG. 3C

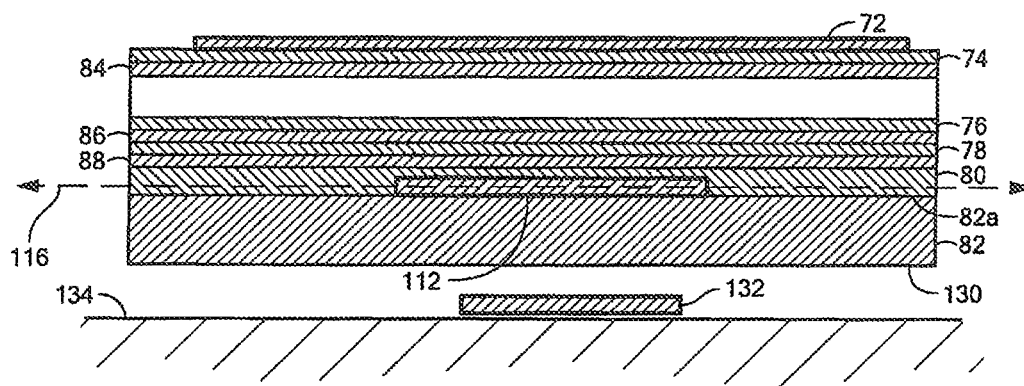


FIG. 3D

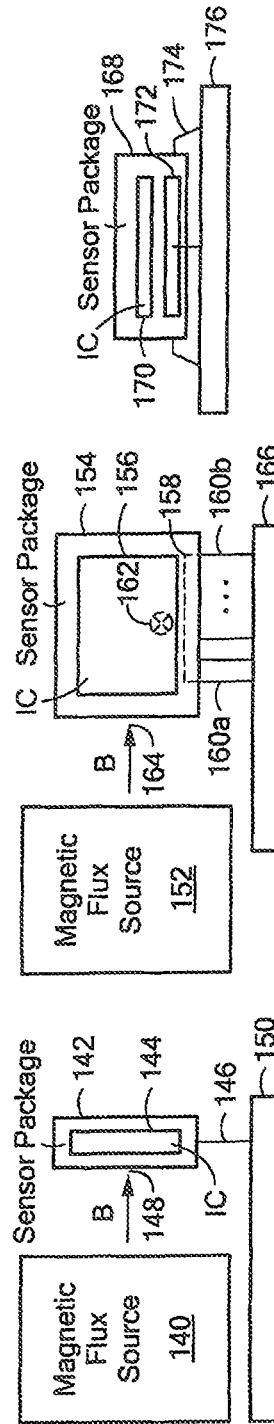


FIG. 3E

FIG. 3F

FIG. 3G

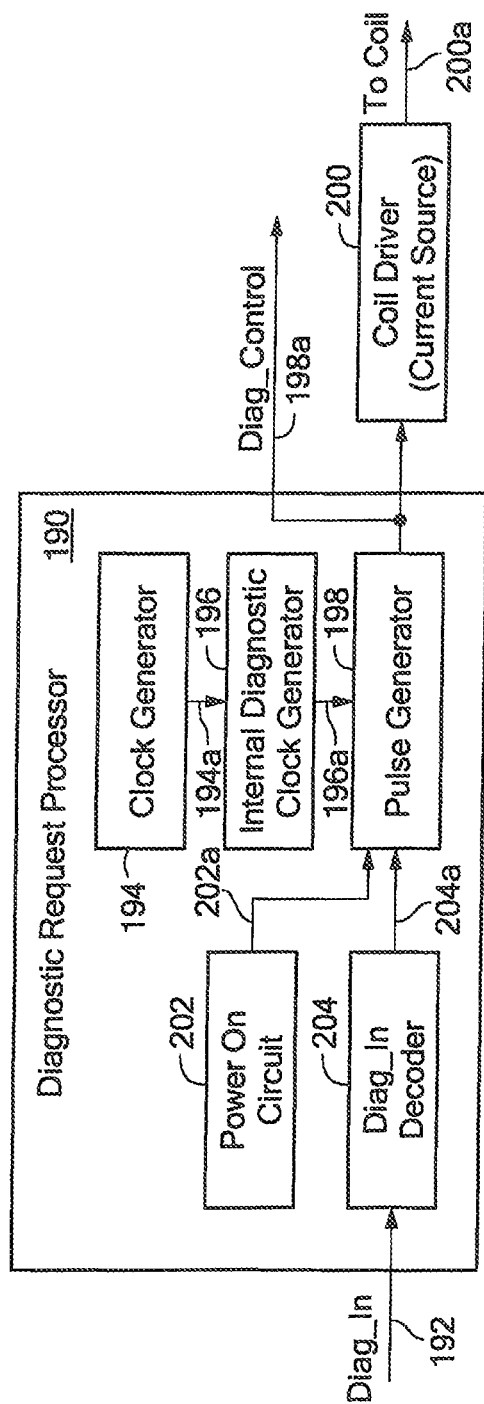


FIG. 4

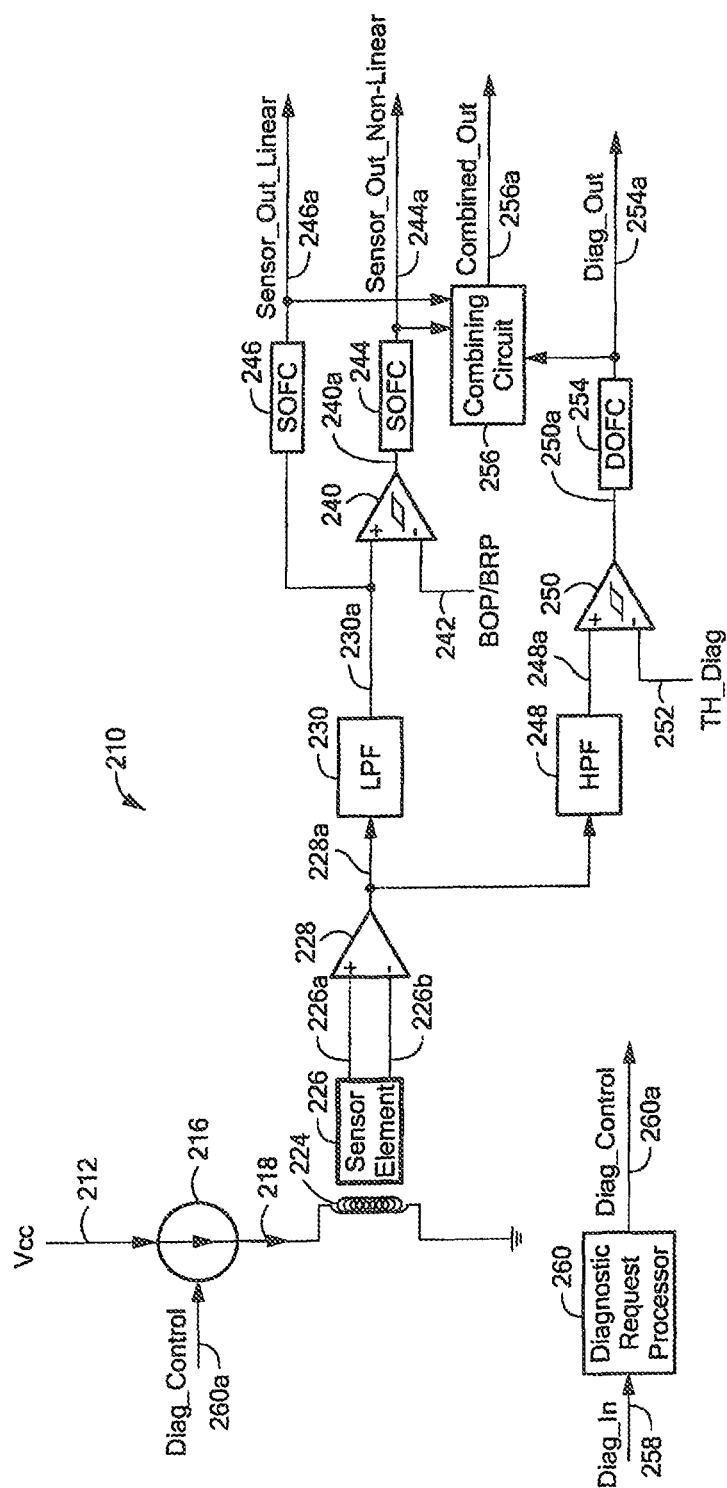


FIG. 5

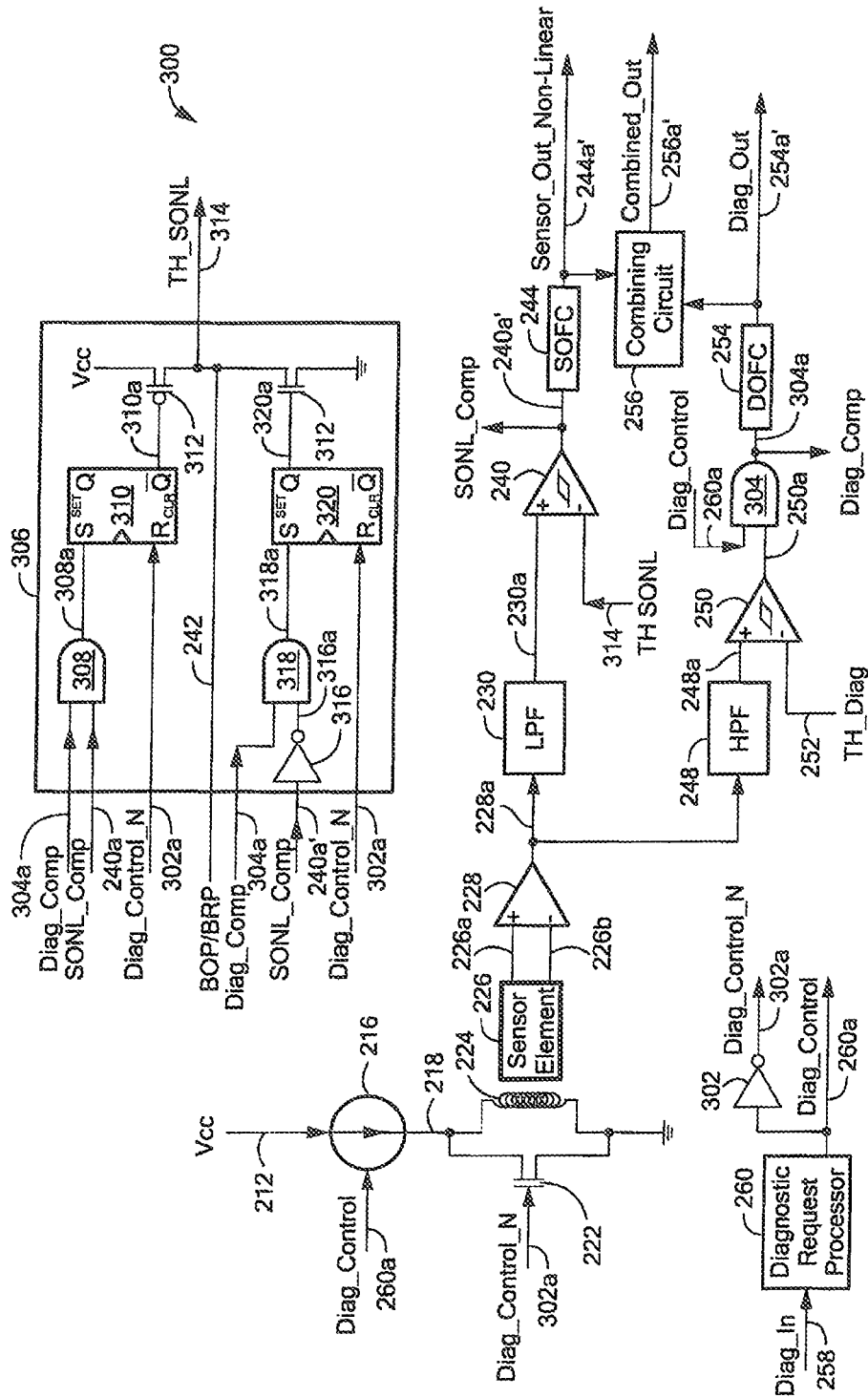


FIG. 5A

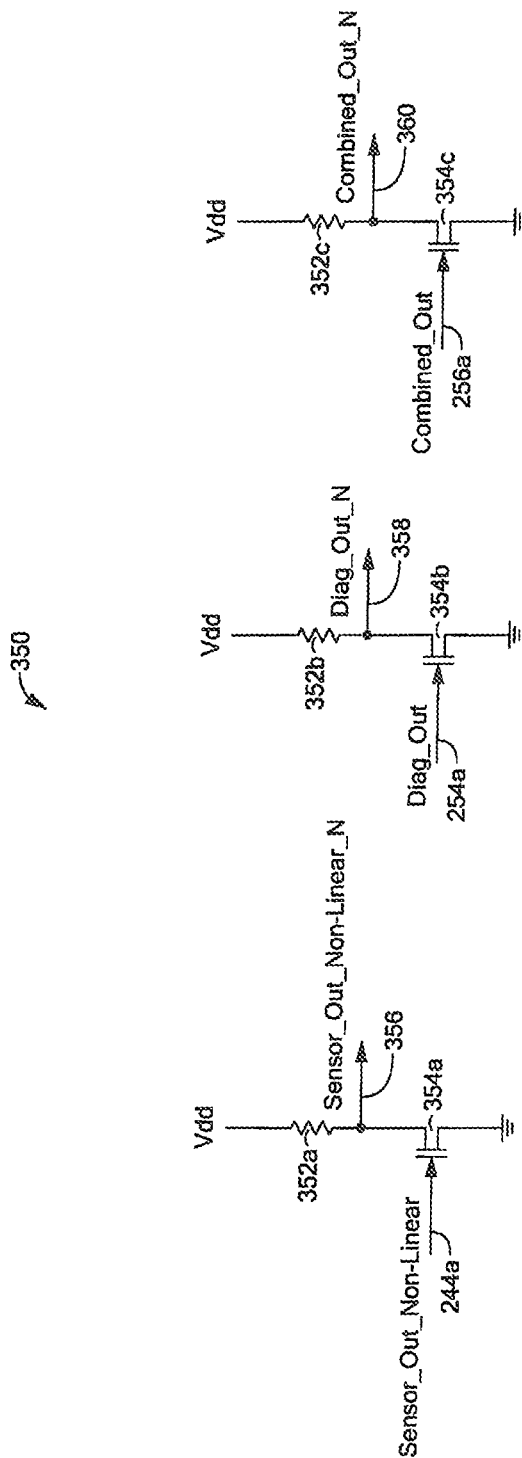


FIG. 5B

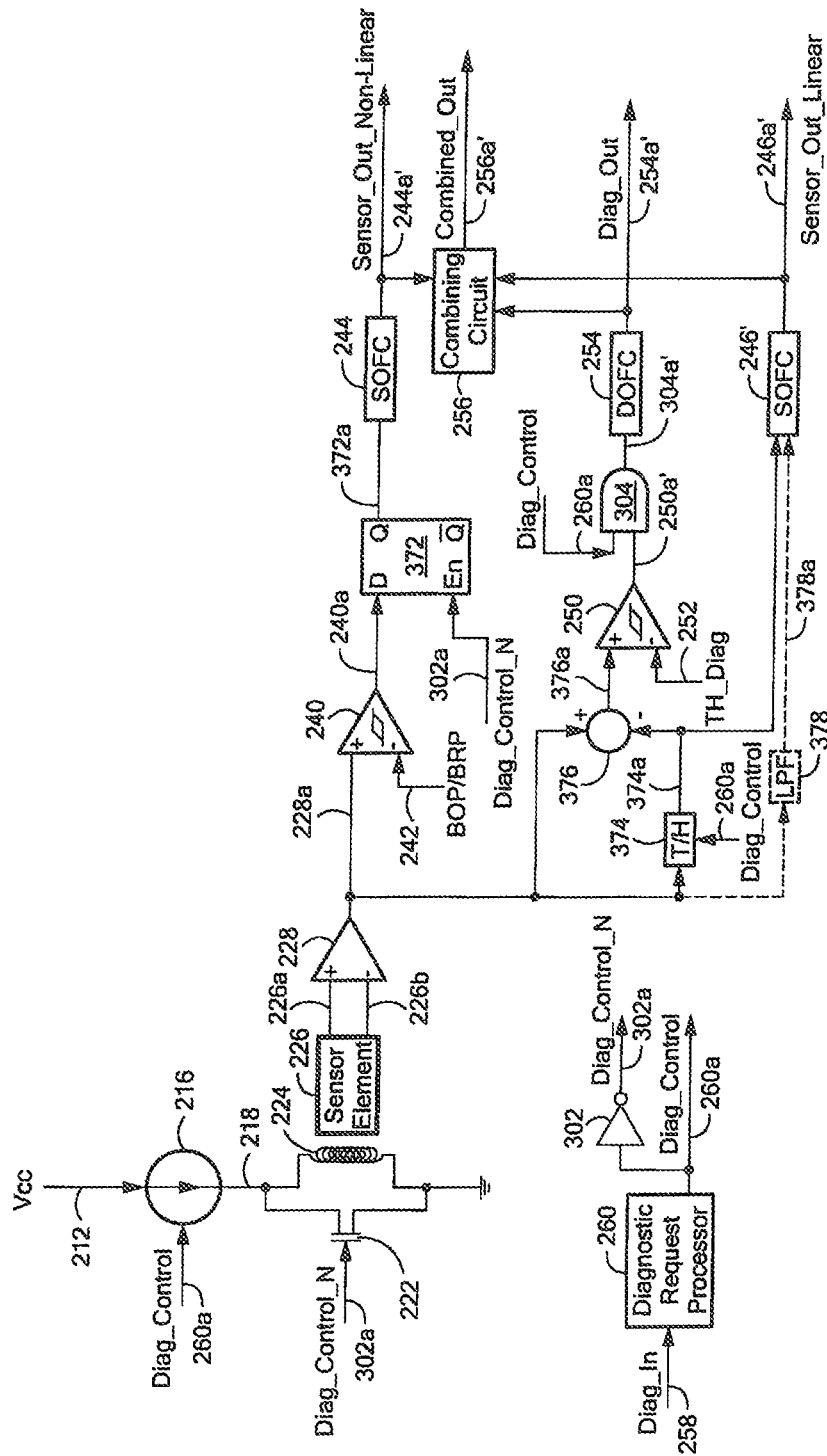
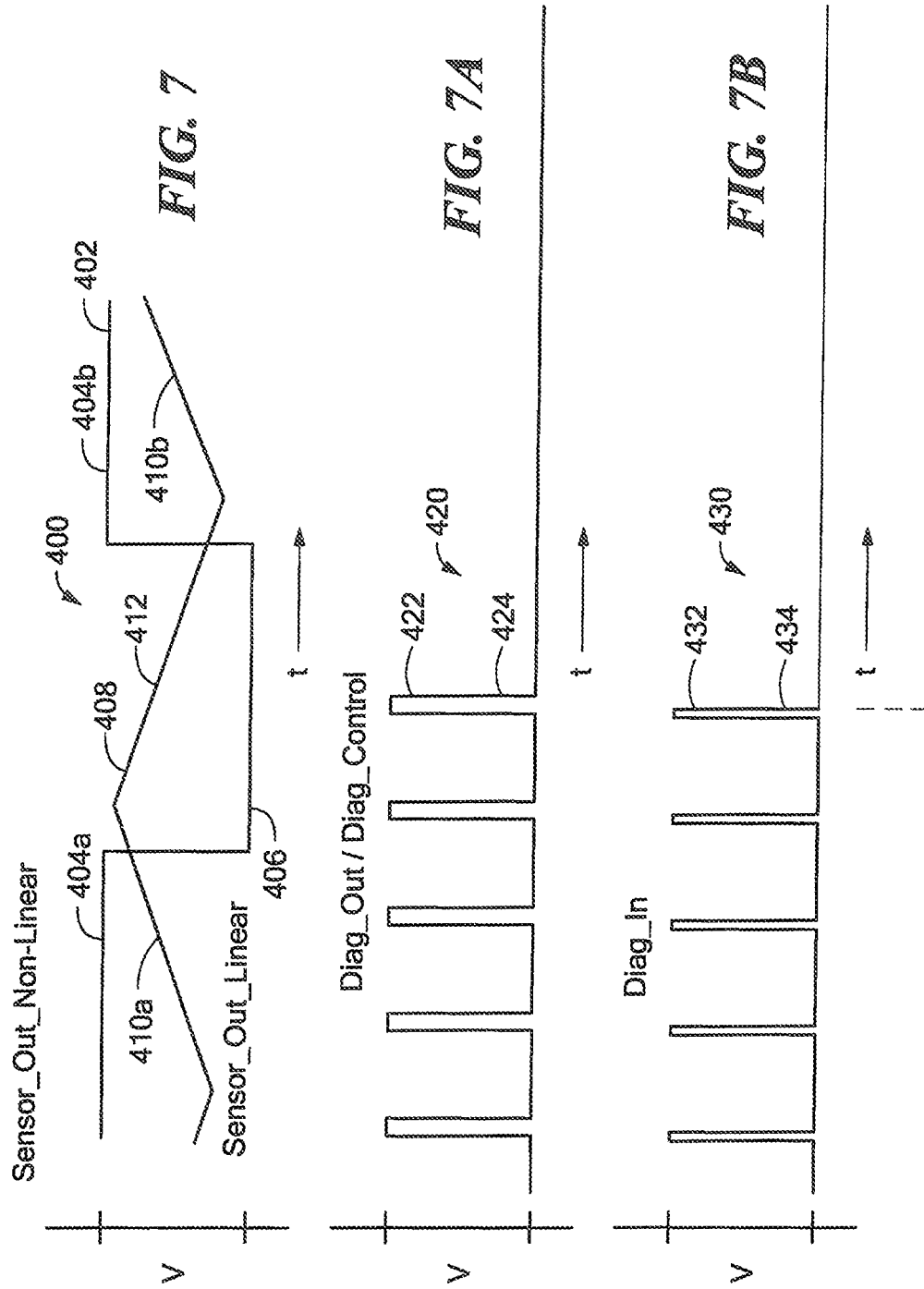
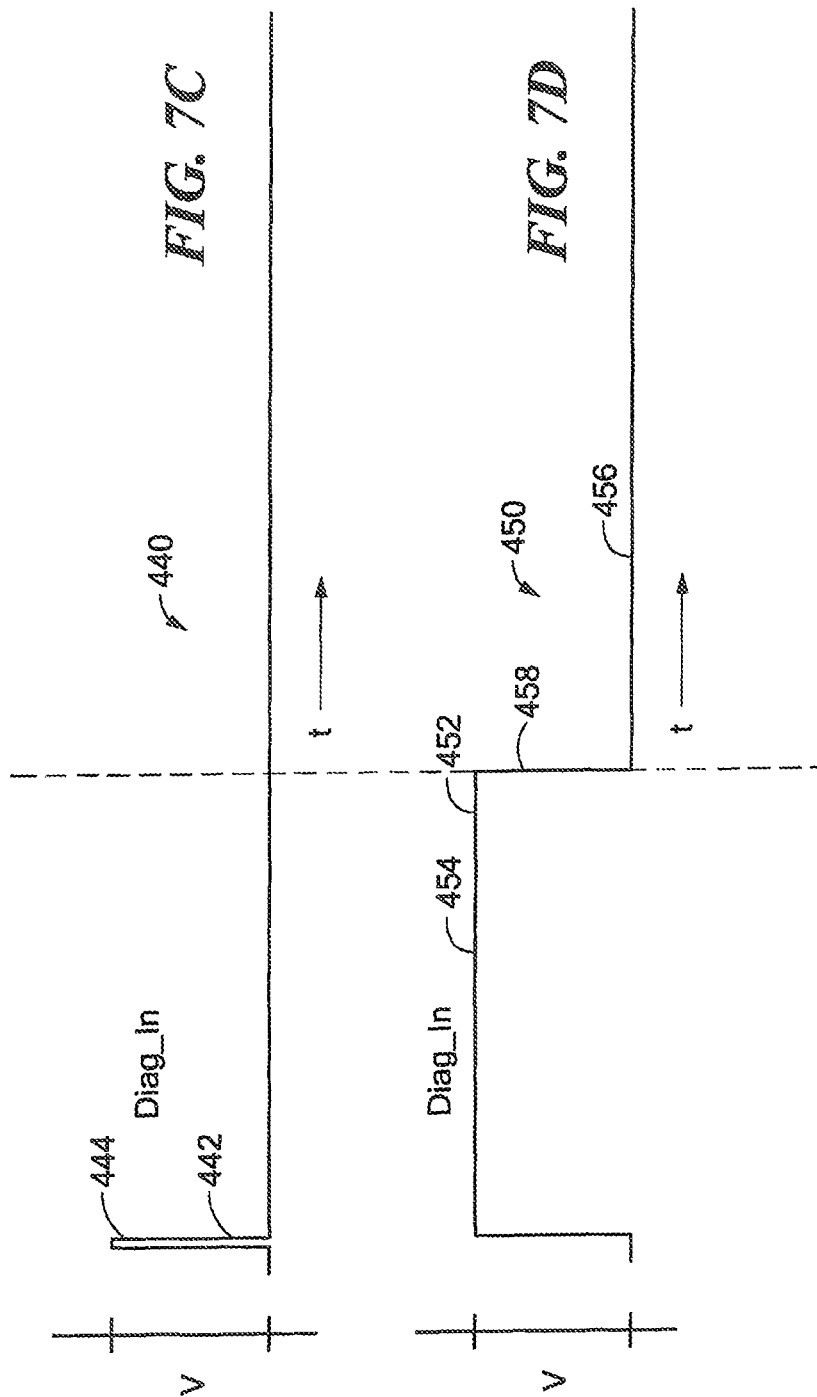
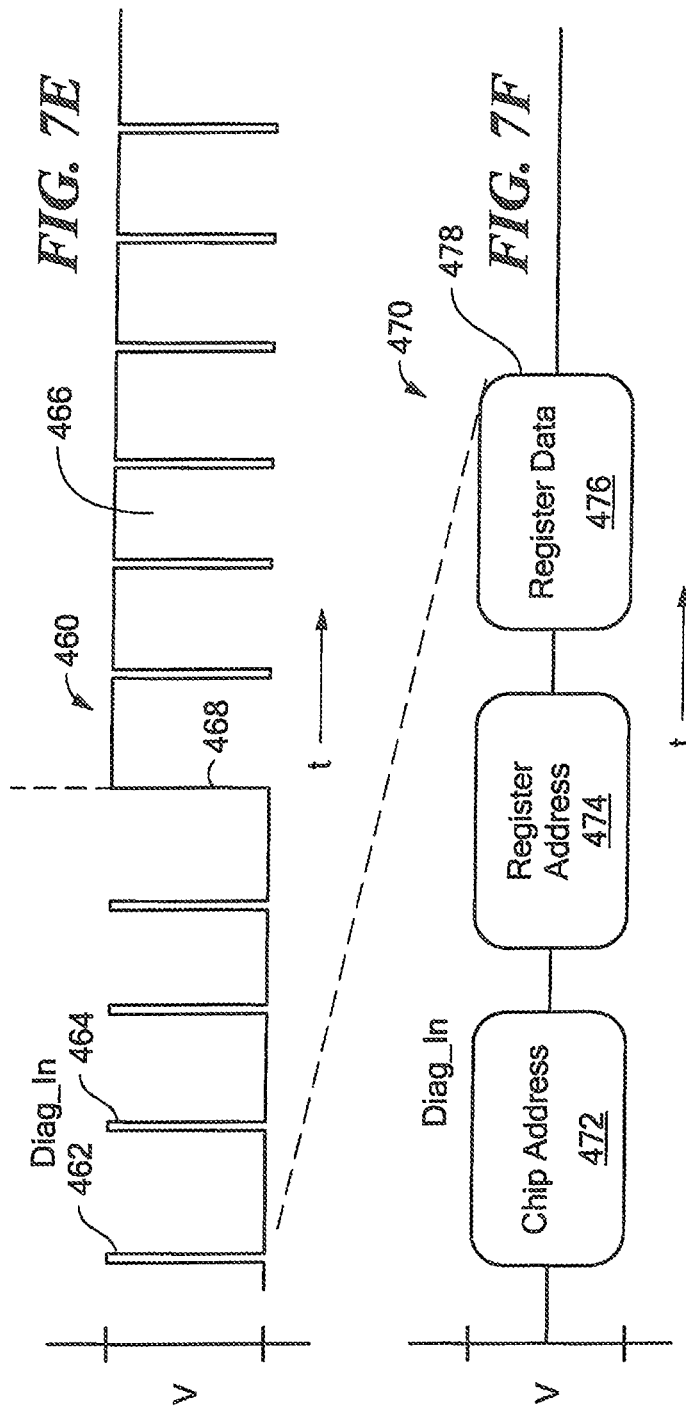
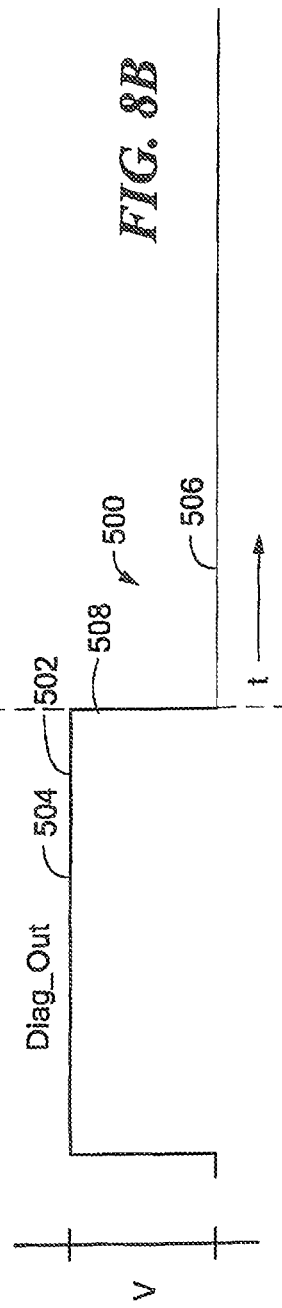
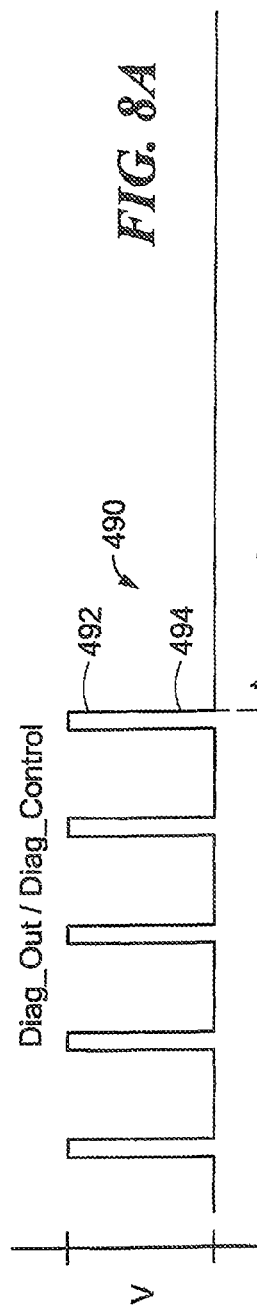
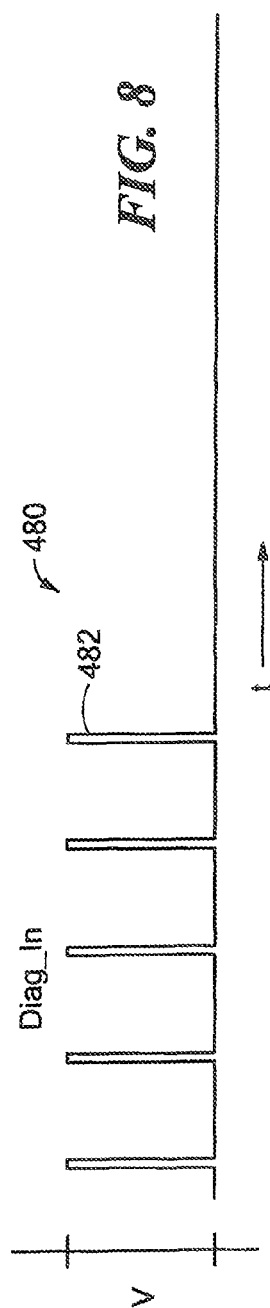


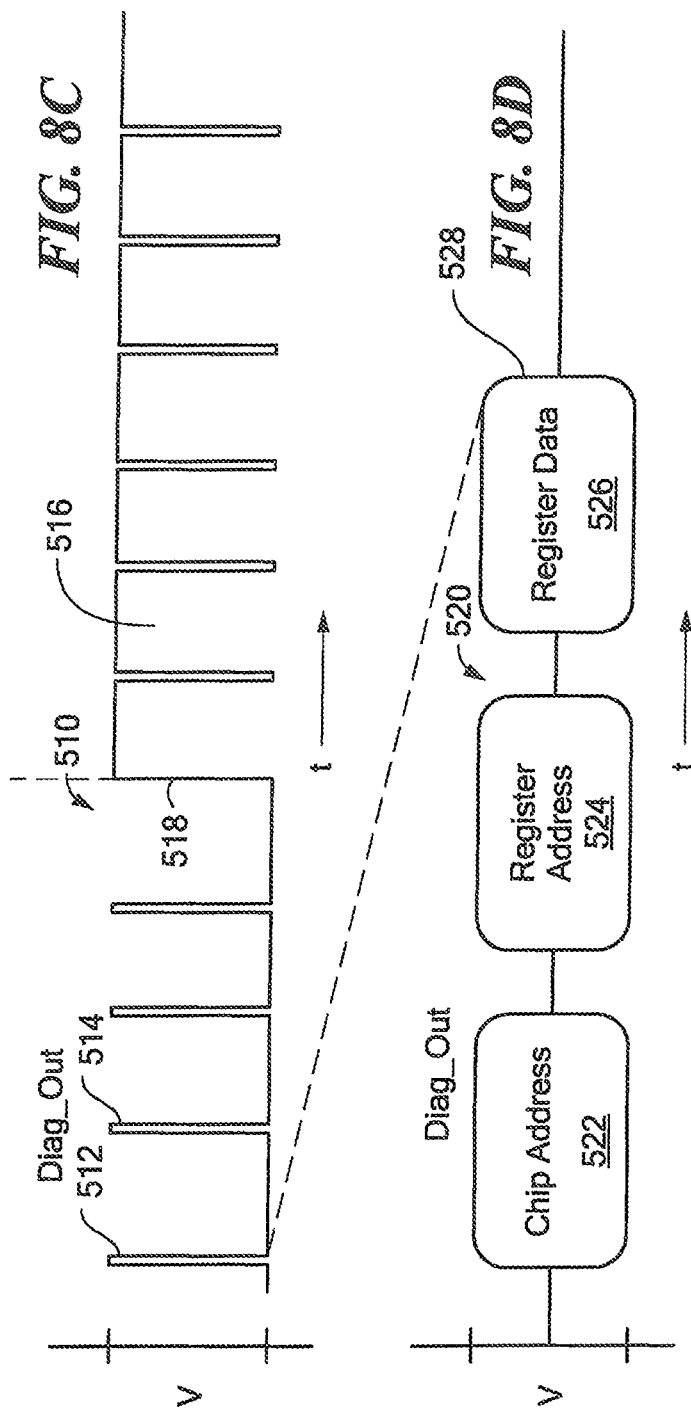
FIG. 6

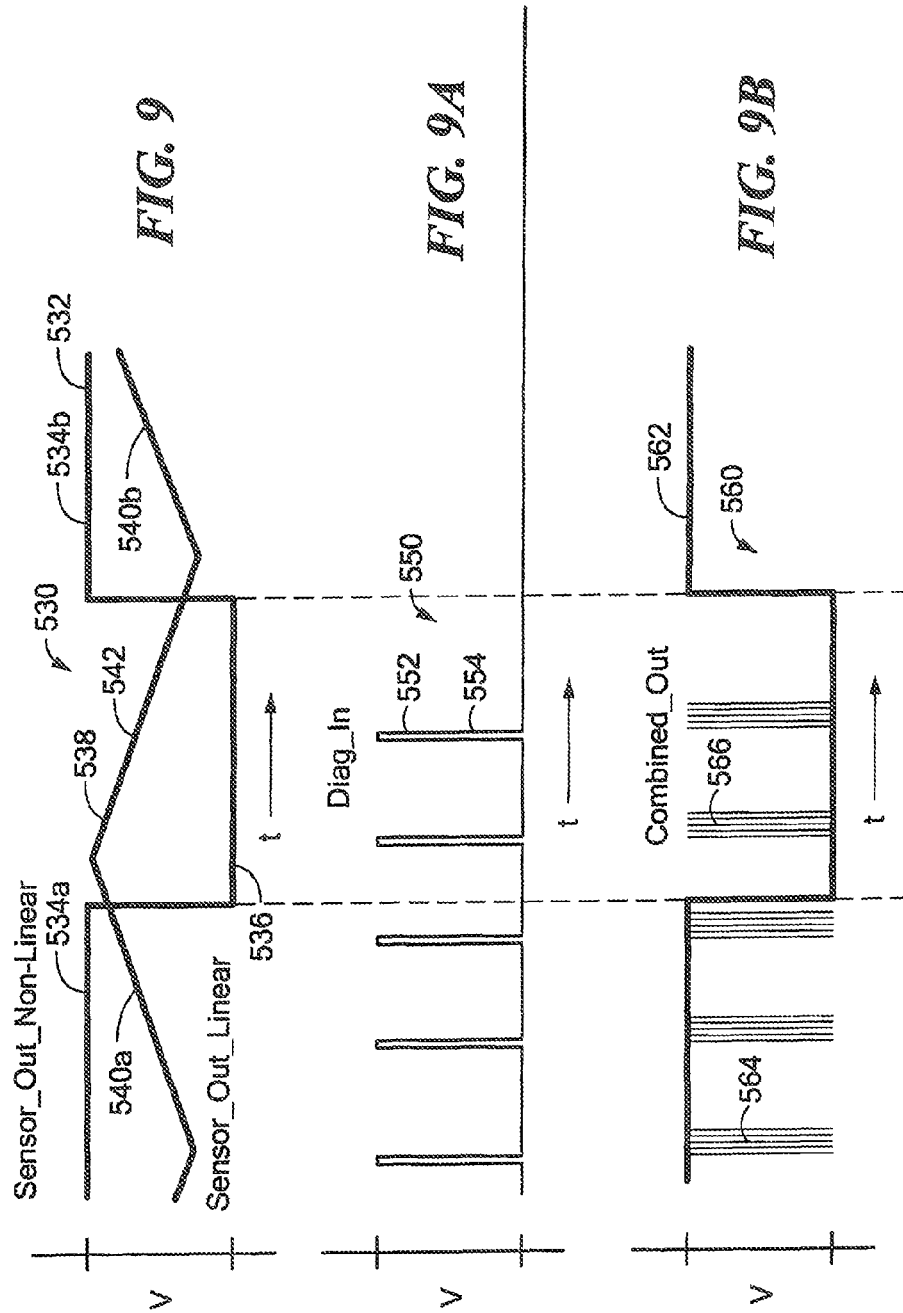


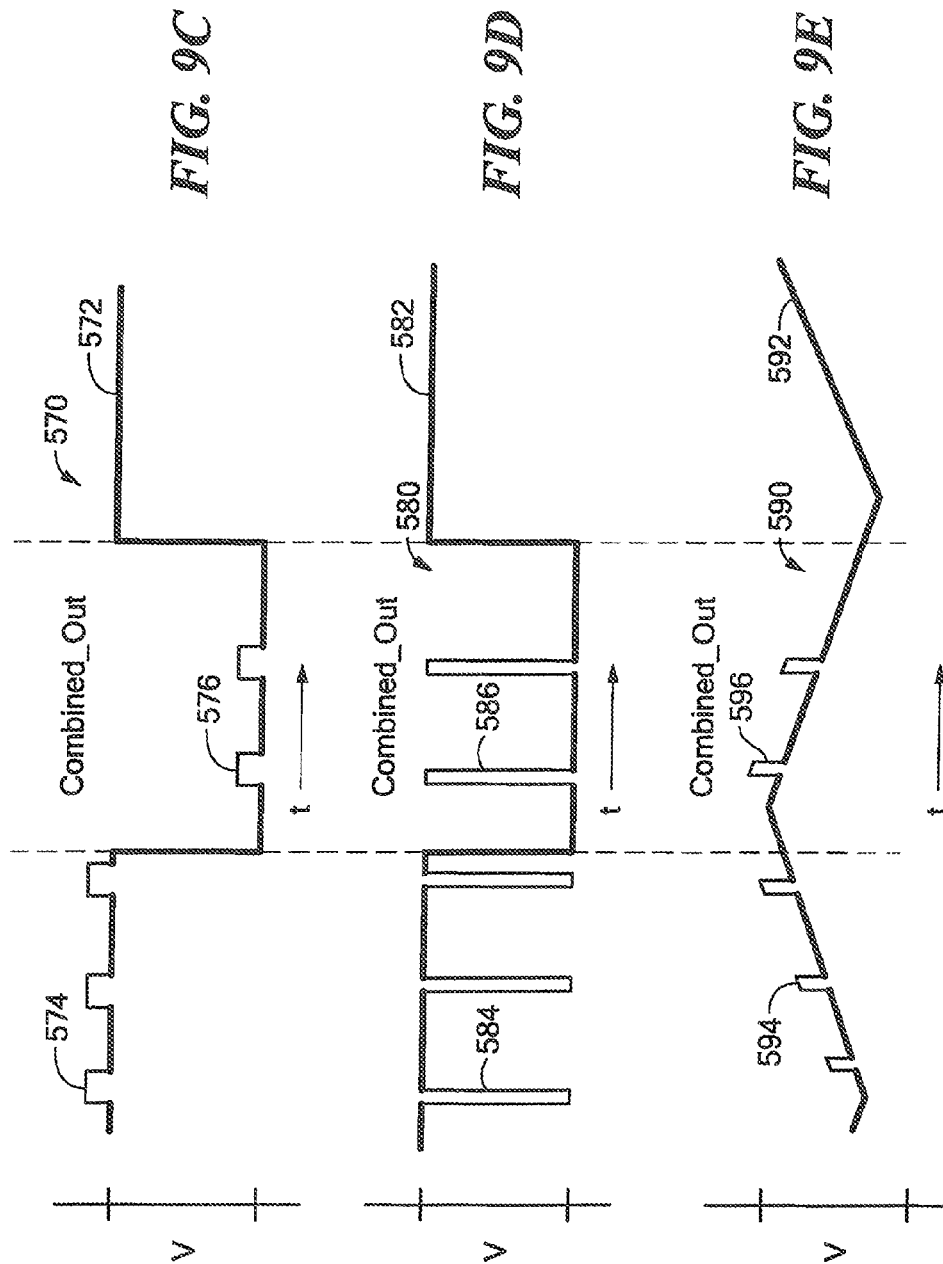


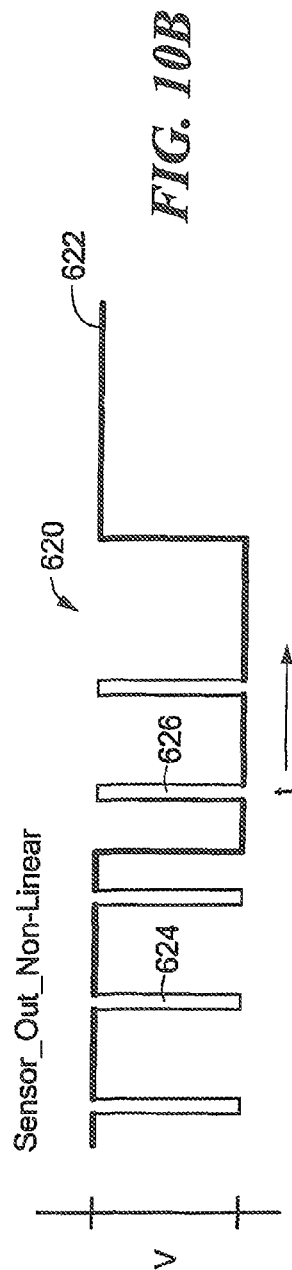
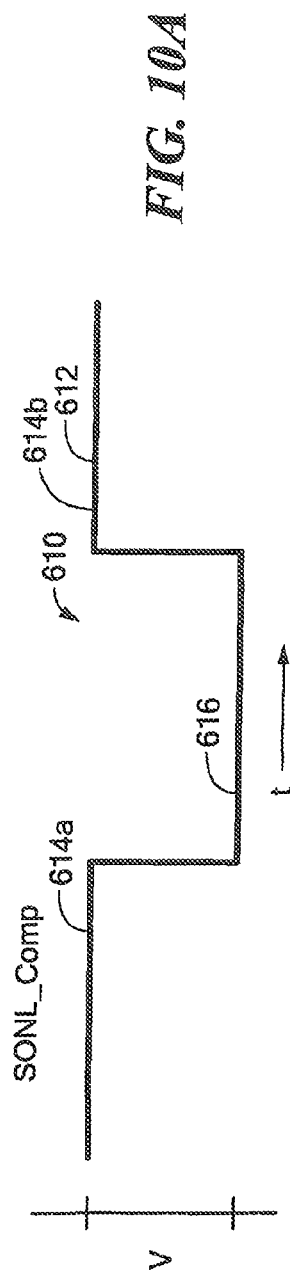
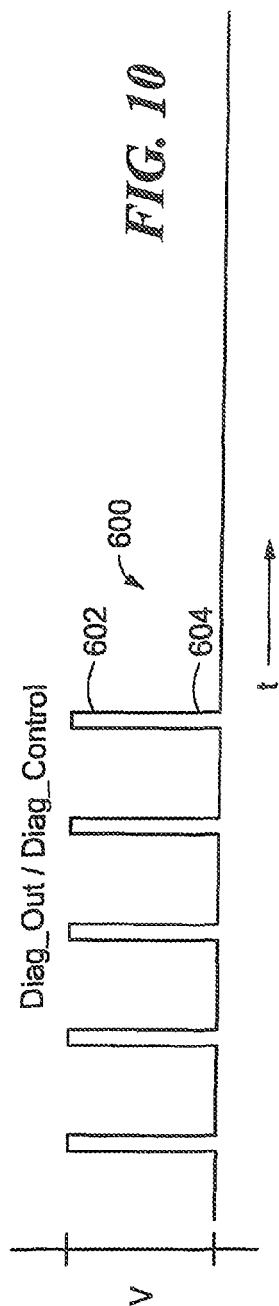












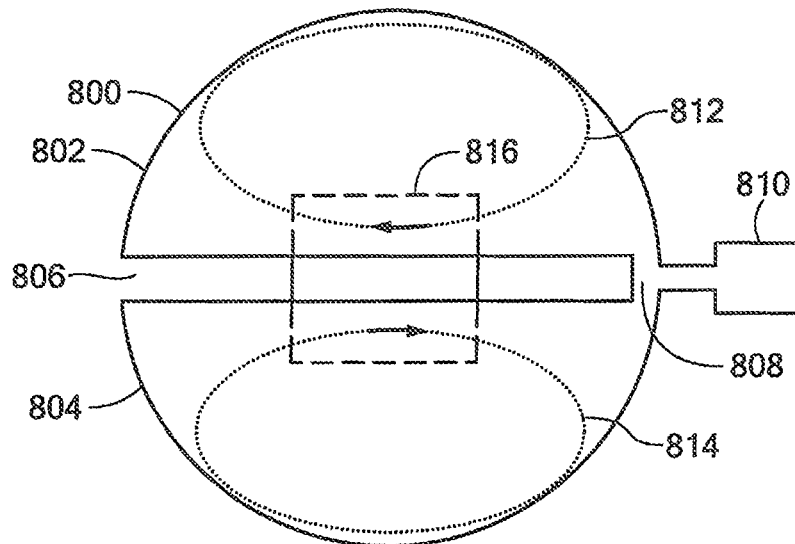


FIG. 11

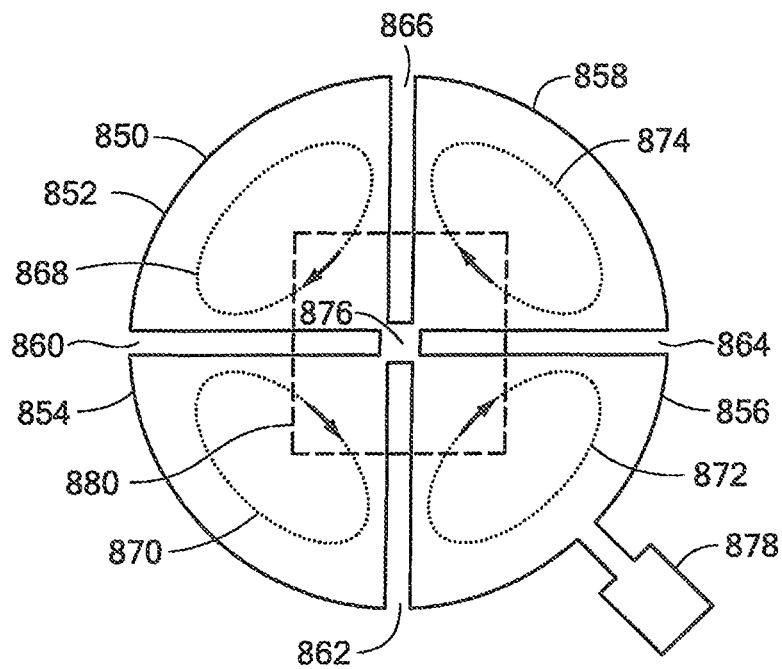
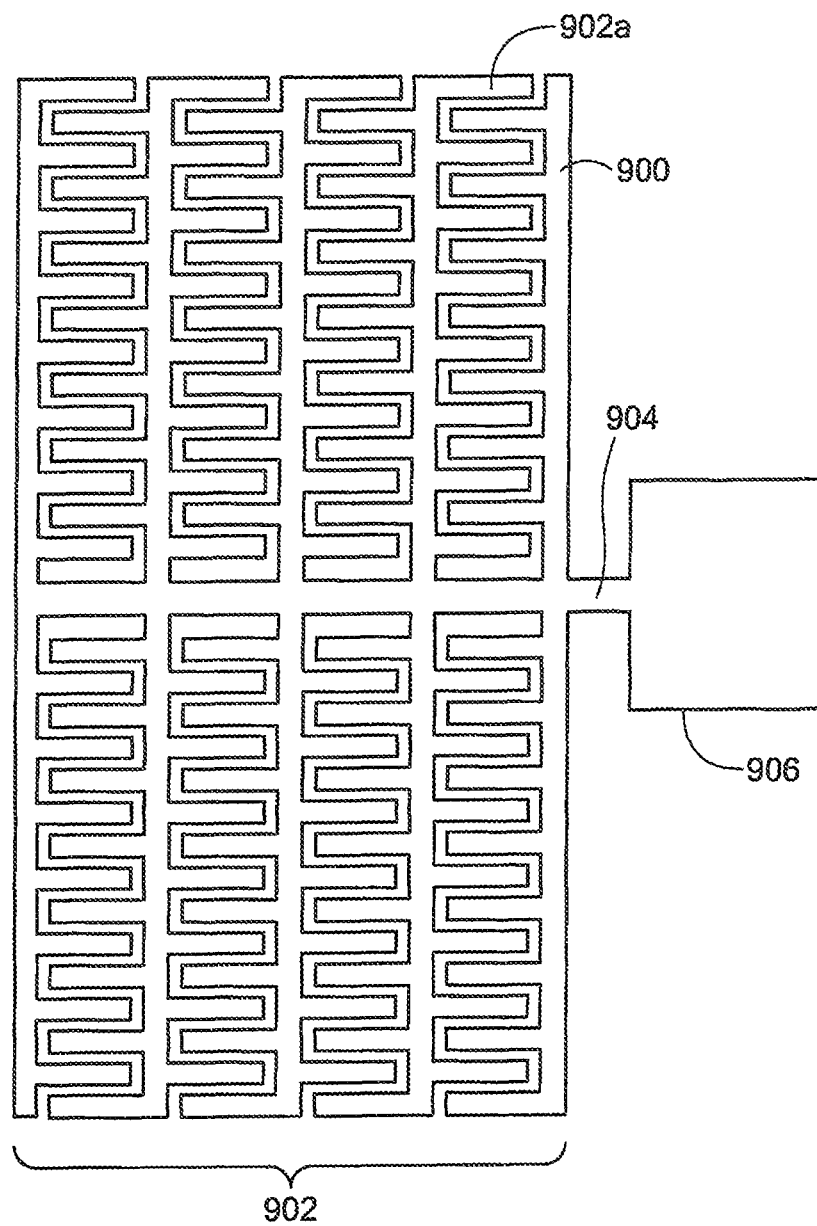


FIG. 12

**FIG. 13**

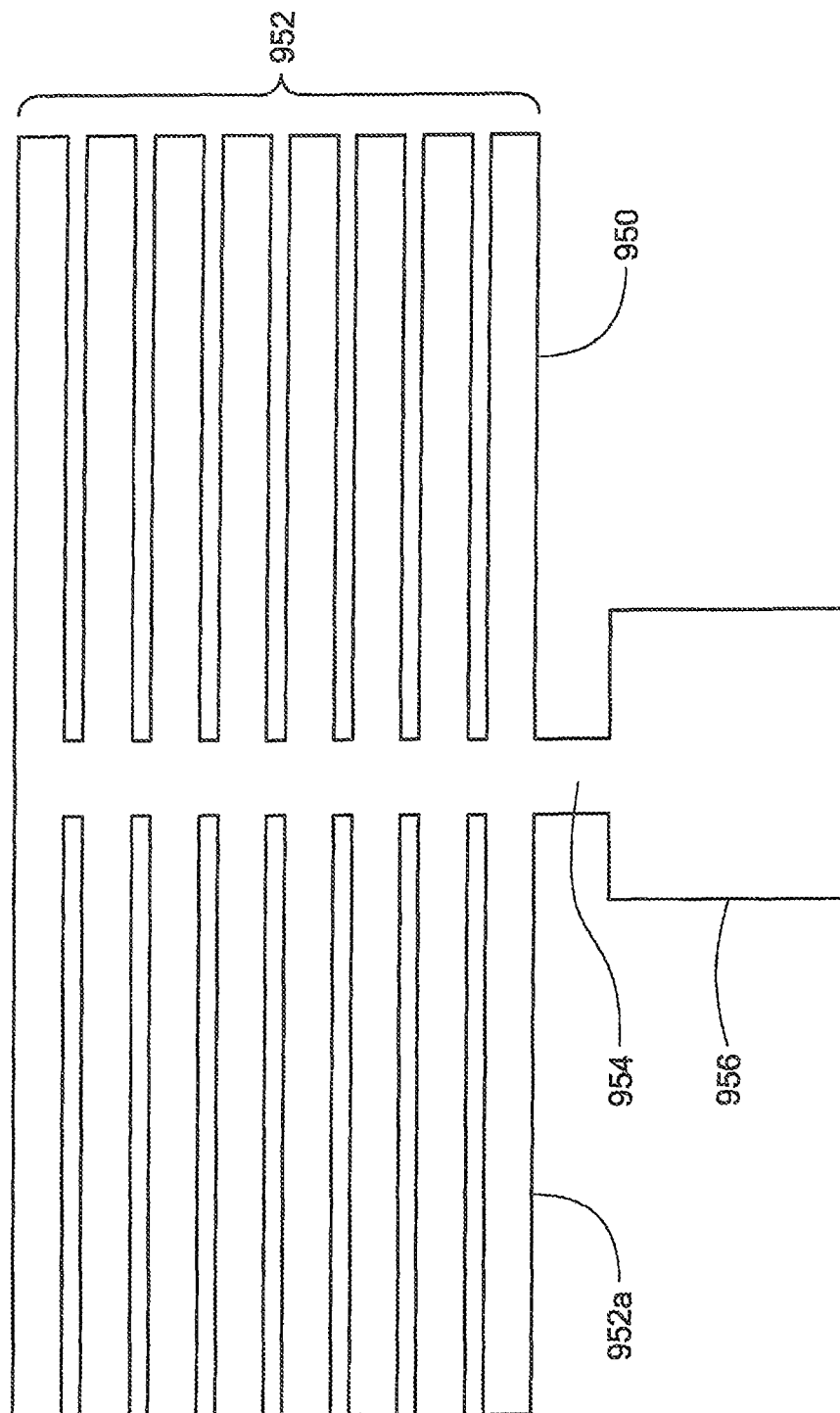


FIG. 14

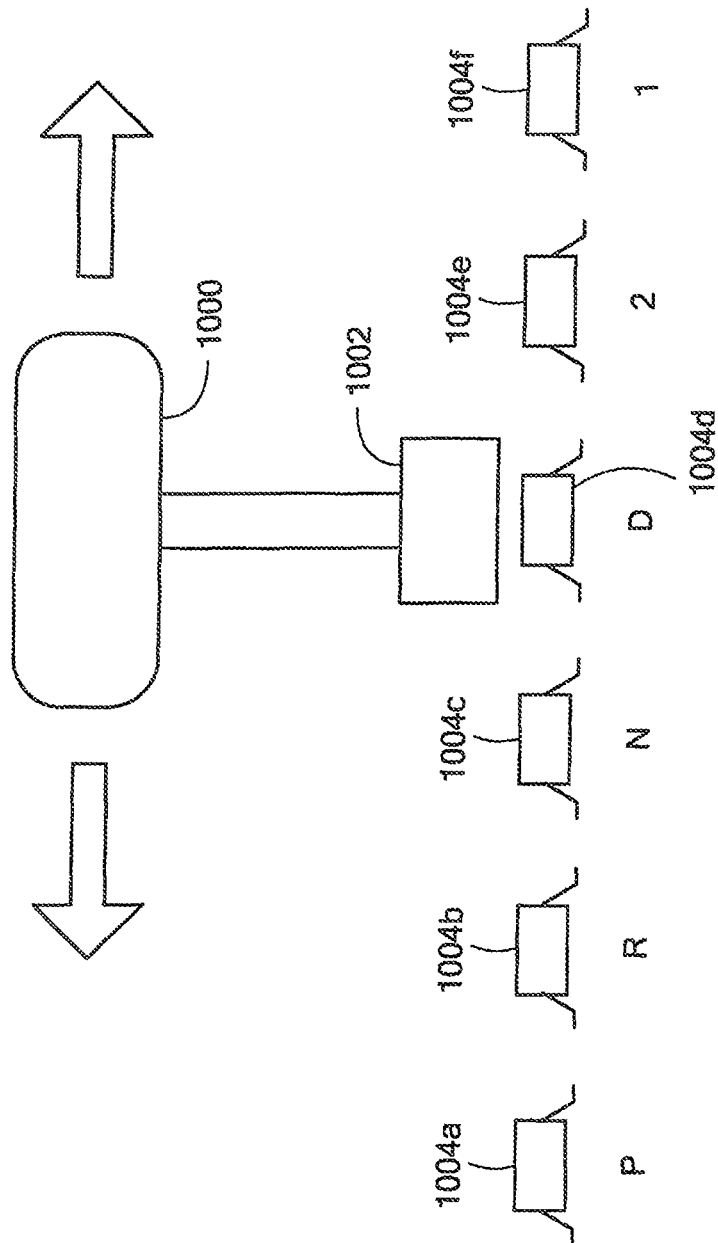


FIG. 15

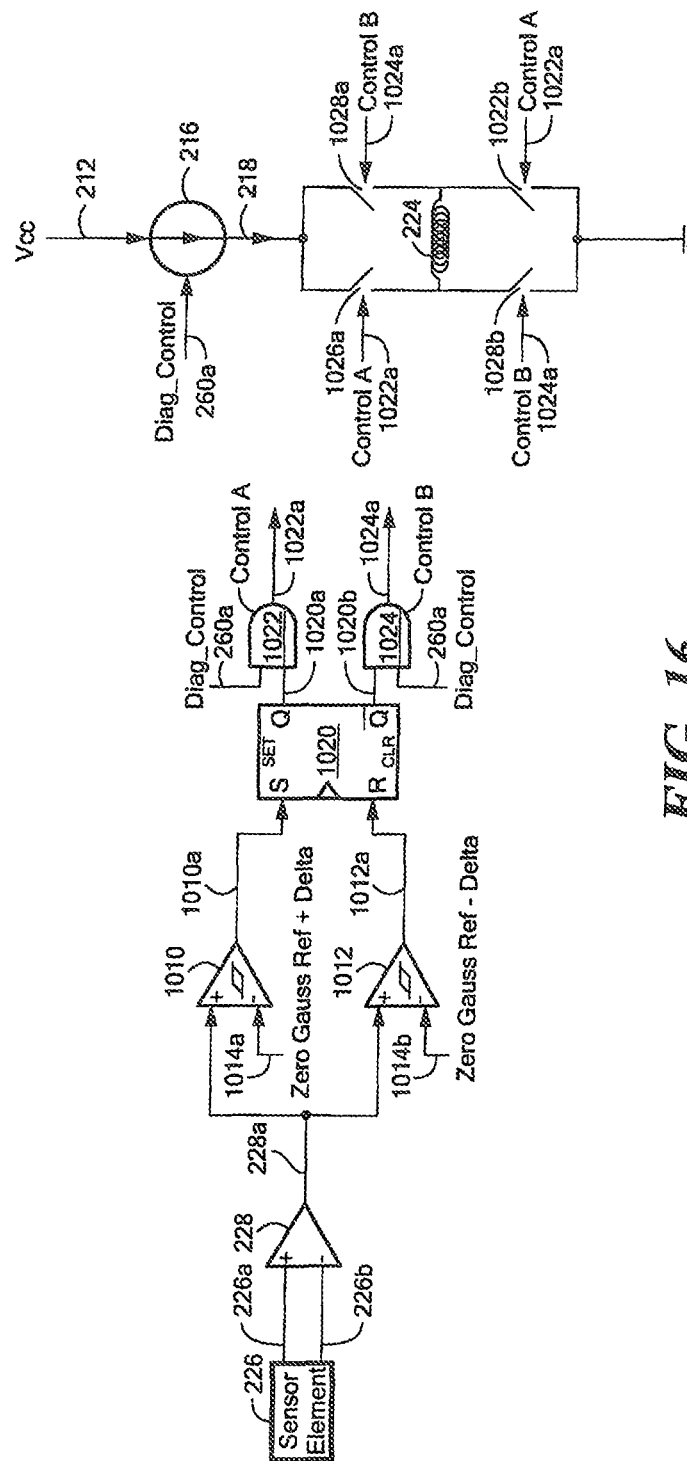


FIG. 16

1

CIRCUITS AND METHODS FOR GENERATING A SELF-TEST OF A MAGNETIC FIELD SENSOR

CROSS REFERENCE TO RELATED APPLICATIONS

This application is a Continuation Application of U.S. patent application Ser. No. 13/743,451, filed Jan. 17, 2013, now U.S. Pat. No. 8,818,749, issued Aug. 26, 2014, which application is a Continuation Application of U.S. patent application Ser. No. 12/706,318, filed Feb. 16, 2010, now U.S. Pat. No. 8,447,556, issued May 21, 2013, which application claims the benefit under 35 U.S.C. §119(e) of U.S. Provisional Application No. 61/153,059 filed Feb. 17, 2009, which applications are incorporated herein by reference in their entirety.

STATEMENT REGARDING FEDERALLY SPONSORED RESEARCH

Not Applicable.

FIELD OF THE INVENTION

This invention relates generally to magnetic field sensors and, more particularly, to a magnetic field sensors having a self-test capability.

BACKGROUND OF THE INVENTION

As is known, there are a variety of types of magnetic field sensing elements, including, but not limited to, Hall effect elements, magnetoresistance elements, and magnetotransistors. As is also known, there are different types of Hall effect elements, for example, a planar Hall element, a vertical Hall element, and a circular Hall element. As is also known, there are different types of magnetoresistance elements, for example, a giant magnetoresistance (GMR) element, an anisotropic magnetoresistance element (AMR), a tunneling magnetoresistance (TMR) element, and a magnetic tunnel junction (MTJ).

Hall effect elements generate an output voltage proportional to a magnetic field. In contrast, magnetoresistance elements change resistance in proportion to a magnetic field. In a circuit, an electrical current can be directed through the magnetoresistance element, thereby generating a voltage output signal proportional to the magnetic field.

Magnetic field sensors, i.e., circuits that use magnetic field sensing elements, are used in a variety of applications, including, but not limited to, a current sensor that senses a magnetic field generated by a current carried by a current-carrying conductor, a magnetic switch that senses the proximity of a ferromagnetic object, a rotation detector that senses passing ferromagnetic articles, for example magnetic domains of a ring magnet, and a magnetic field sensor that senses a magnetic field density of a magnetic field.

As is known, some integrated circuits have internal built-in self-test (BIST) capabilities. A built-in self-test is a function that can verify all or a portion of the internal functionality of an integrated circuit. Some types of integrated circuits have built-in self-test circuits built directly onto the integrated circuit die. Typically, the built-in self-test is activated by external means, for example, a signal communicated from outside the integrated circuit to dedicated pins or ports on the integrated circuit. For example, an integrated circuit that has a memory portion can include a built-in self-test circuit,

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which can be activated by a self-test signal communicated from outside the integrated circuit. The built-in self-test circuit can test the memory portion of the integrated circuit in response to the self-test signal.

Conventional built-in self-test circuits tend not to allow the integrated circuit to perform its intended function while the built-in self-test is being performed. Instead, during the built-in self-test, the built-in self-test circuit exercises all of, or parts of, circuits on the integrated circuit in particular ways that do not necessarily allow concurrent operation of functions that the integrated circuit is intended to perform. Therefore, the built-in self-test is typically only activated one time, for example, upon power up of the integrated circuit, or from time to time. At other times, the built-in self-test circuit and function are dormant and the integrated circuit can perform its intended function.

Furthermore, when used in magnetic field sensors, conventional built-in self-test circuits tend not to test the magnetic field sensing element used in the magnetic field sensor.

It would be desirable to provide built in self-test circuits and techniques in a magnetic field sensor that allow the self-test to be run from time to time or upon command while the magnetic field sensor concurrently performs its intended function. It would also be desirable to provide such a concurrent self-test that tests a magnetic field sensing element used within the magnetic field sensor.

SUMMARY OF THE INVENTION

The present invention provides self-test circuits and techniques in a magnetic field sensor that allow the self-test to be run from time to time or upon command while the magnetic field sensor concurrently performs its intended function. The present invention also provides such a concurrent self-test that tests a magnetic field sensing element used within the magnetic field sensor.

In accordance with one aspect of the present invention, a magnetic field sensor includes a magnetic field sensing element supported by a substrate. The magnetic field sensing element is for generating a composite magnetic field signal having a measured-magnetic-field-responsive signal portion and a self-test-responsive signal portion. The measured-magnetic-field-responsive signal portion is responsive to a measured magnetic field. The self-test-responsive signal portion is responsive to a self-test magnetic field. The magnetic field sensor also includes a self-test circuit having a self-test current conductor proximate to the magnetic field sensing element. The self-test current conductor is for carrying a self-test current to generate the self-test magnetic field. The magnetic field sensor also includes a processing circuit coupled to receive a signal representative of the composite magnetic field signal. The processing circuit is configured to generate a sensor signal representative of the measured-magnetic-field-responsive signal portion. The processing circuit is also configured to generate at least one of a diagnostic signal representative of the self-test-responsive signal portion or a composite signal representative of both the measured-magnetic-field-responsive signal portion and the self-test-responsive signal portion.

In accordance with another aspect of the present invention, a method of generating a self-test of a magnetic field sensor includes generating, with a magnetic field sensing element, a composite magnetic field signal comprising a measured-magnetic-field-responsive signal portion and a self-test-responsive signal portion. The measured-magnetic-field-responsive signal portion is responsive to a measured magnetic field. The self-test-responsive signal portion is responsive to

a self-test magnetic field. The method also includes generating a self-test current in a self-test current conductor proximate to the magnetic field sensing element. The self-test current conductor is for carrying the self-test current to generate the self-test magnetic field. The method also includes generating a sensor output signal representative of the measured-magnetic-field-responsive signal portion. The method also includes generating at least one of a diagnostic signal representative of the self-test-responsive signal portion or a composite signal representative of both the measured-magnetic-field-responsive signal portion and the self-test-responsive signal portion.

BRIEF DESCRIPTION OF THE DRAWINGS

The foregoing features of the invention, as well as the invention itself may be more fully understood from the following detailed description of the drawings, in which:

FIG. 1 is block diagram showing a magnetic field sensor in accordance with the present invention, having a magnetic field sensing element, a self-test conductor, a diagnostic request processor, a signal processor, and output circuits;

FIG. 2 is a block diagram showing one exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1;

FIG. 2A is a block diagram showing another exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1;

FIG. 2B is a block diagram showing yet another exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1;

FIG. 2C is a block diagram showing yet another exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1;

FIG. 2D is a block diagram showing yet another exemplary arrangement of the magnetic field sensing element, here shown as four magnetic field sensing elements, and the self-test conductor of FIG. 1;

FIG. 3 is block diagram showing a cross section representative of one exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1, namely, the magnetic field sensing element and the self-test conductor of FIG. 2B, wherein the arrangement includes an electromagnetic shield;

FIG. 3A is block diagram showing a cross section representative of another exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1, wherein the arrangement includes an electromagnetic shield;

FIG. 3B is block diagram showing a cross section representative of yet another exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1;

FIG. 3C is block diagram showing a cross section representative of yet another exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1, namely, the magnetic field sensing element and the self-test conductor of FIG. 2C, wherein the arrangement includes an electromagnetic shield;

FIG. 3D is block diagram showing a cross section representative of yet another exemplary arrangement of the magnetic field sensing element and the self-test conductor of FIG. 1, wherein the arrangement includes an electromagnetic shield;

FIGS. 3E-3G are block diagrams showing three arrangements for magnetic field sensors;

FIG. 4 is a block diagram showing further details of the diagnostic request processor of FIG. 1;

FIG. 5 is a block diagram of an exemplary magnetic field sensor showing further details of the magnetic field sensing element, the self-test conductor, and the signal processor of FIG. 1;

FIG. 5A is a block diagram of another exemplary magnetic field sensor showing further details of the magnetic field sensing element, the self-test conductor, and the signal processor of FIG. 1;

FIG. 5B is a block diagram showing common drain output circuits that can be used as part of the magnetic field sensors of FIGS. 5 and 5A;

FIG. 6 is a block diagram of another exemplary magnetic field sensor showing further details of the magnetic field sensing element, the self-test conductor, and the signal processor of FIG. 1;

FIG. 7 is a graph showing exemplary output signals from the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIG. 7A is a graph showing another exemplary output signal from the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIGS. 7B-7F are graphs showing different exemplary diagnostic input signals received by the diagnostic request processor of the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIG. 8 is a graph showing a diagnostic input signal, the same as or similar to the diagnostic input signal of FIG. 7B, received by the diagnostic request processor of the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIGS. 8A-8D are graphs showing different exemplary diagnostic output signals generated by the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIG. 9 is a graph showing exemplary output signals, the same as or similar to the output signals shown in FIG. 7, from the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIG. 9A is a graph showing a diagnostic input signal, the same as or similar to the diagnostic input signal of FIGS. 7B and 8, received by the diagnostic request processor of the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIGS. 9B-9E are graphs showing different exemplary combined output signals generated by the magnetic field sensors of FIGS. 1, 5, 5A, and 6;

FIGS. 10-10B are a series of graph showing a diagnostic control signal, a diagnostic output signal generated by the magnetic field sensors of FIGS. 5 and 6, and a diagnostic output signal generated by the magnetic field sensor of FIG. 5A;

FIG. 11 is a top view of an exemplary electromagnetic shield that can form part of the magnetic field sensor of FIG. 1, and which can be used as the electromagnetic shield of FIGS. 3, 3A, 3C, and 3D;

FIG. 12 is a top view of another exemplary electromagnetic shield that can form part of the magnetic field sensor of FIG. 1, and which can be used as the electromagnetic shield of FIGS. 3, 3A, 3C, and 3D;

FIG. 13 is a top view of yet another exemplary electromagnetic shield that can form part of the magnetic field sensor of FIG. 1, and which can be used as the electromagnetic shield of FIGS. 3, 3A, 3C, and 3D;

FIG. 14 is a top view of yet another exemplary electromagnetic shield that can form part of the magnetic field sensor of FIG. 1, and which can be used as the electromagnetic shield of FIGS. 3, 3A, 3C, and 3D;

FIG. 15 is a block diagram showing a plurality of magnetic field sensors used to sense a position of a gear shift lever as may be provided in an automobile; and

FIG. 16 is a block diagram of a circuit having a self-test conductor, through which a direction of a drive current can be changed.

DETAILED DESCRIPTION OF THE INVENTION

Before describing the present invention, some introductory concepts and terminology are explained. As used herein, the term “magnetic field sensing element” is used to describe a variety of electronic elements that can sense a magnetic field. The magnetic field sensing elements can be, but are not limited to, Hall effect elements, magnetoresistance elements, or magnetotransistors. As is known, there are different types of Hall effect elements, for example, a planar Hall element, a vertical Hall element, and a circular Hall element. As is also known, there are different types of magnetoresistance elements, for example, a giant magnetoresistance (GMR) element, an anisotropic magnetoresistance element (AMR), a tunneling magnetoresistance (TMR) element, an Indium antimonide (InSb) sensor, and a magnetic tunnel junction (MTJ).

As is known, some of the above-described magnetic field sensing elements tend to have an axis of maximum sensitivity parallel to a substrate that supports the magnetic field sensing element, and others of the above-described magnetic field sensing elements tend to have an axis of maximum sensitivity perpendicular to a substrate that supports the magnetic field sensing element. In particular, most types of magnetoresistance elements tend to have axes of maximum sensitivity parallel to the substrate and most types of Hall elements tend to have axes of sensitivity perpendicular to a substrate.

As used herein, the term “magnetic field sensor” is used to describe a circuit that includes a magnetic field sensing element. Magnetic field sensors are used in a variety of applications, including, but not limited to, a current sensor that senses a magnetic field generated by a current carried by a current-carrying conductor, a magnetic switch that senses the proximity of a ferromagnetic object, a rotation detector that senses passing ferromagnetic articles, for example, magnetic domains of a ring magnet, and a magnetic field sensor that senses a magnetic field density of a magnetic field.

Referring to FIG. 1, a magnetic field sensor 10 includes a magnetic field sensing element 32 supported by a substrate (not shown). The magnetic field sensing element 32 is for generating a composite magnetic field signal 32a having a measured-magnetic-field-responsive signal portion and a self-test-responsive signal portion. The measured-magnetic-field-responsive signal portion is responsive to a measured magnetic field. The self-test-responsive signal portion is responsive to a self-test magnetic field. The magnetic field sensor 10 also includes a self-test circuit having a self-test current conductor 30 proximate to the magnetic field sensing element 32. The self-test current conductor 30 is for carrying a self-test current 24a to generate the self-test magnetic field. The magnetic field sensor 10 also includes a processing circuit 34 coupled to receive a signal, e.g., the signal 32a, representative of the composite magnetic field signal 32a. The processing circuit 34 is configured to generate a sensor signal 36a representative of the magnetic field-signal portion. The processing circuit 34 is also configured to generate at least one of a diagnostic signal 36c representative of the self-test-responsive signal portion or a composite signal 36b representative of both the measured-magnetic-field-responsive signal portion and the self-test-responsive signal portion.

In some embodiments, the self-test magnetic field is within a range of about twenty to forty Gauss. However in other embodiments, the self-test magnetic field can be smaller than twenty Gauss or greater than forty Gauss.

The magnetic field sensor 10 can include power and bias and driver circuits 22. The power and bias and driver circuits 22 can include a circuit power and bias module 28 configured to provide various voltages and currents to the rest of the

circuitry within the magnetic field sensor 10. The power and bias and driver circuits 22 can also include a sensor element driver module 26 (e.g., a current source) configured, for example, to generate a current signal 26a coupled to the magnetic field sensing element 32. The power and bias and driver circuits 22 can also include a coil driver module 24 (e.g., a current source) configured to generate a current signal 24a coupled to the self-test current conductor 30. However, in other embodiments, an external coil driver module, apart from the integrated circuit 10 can be used.

The magnetic field sensor 10 can also include a diagnostic request processor 58 coupled to receive a diagnostic input signal (Diag_In) 23. The diagnostic request processor 58 is described more fully below in conjunction with FIG. 4 and the diagnostic input signal 23 is described more fully below in conjunction with FIGS. 4 and 7B-7F. However, let suffice here to say that, in some embodiments, the diagnostic input signal 23 can be decoded by the diagnostic request processor 58, and, in response to the diagnostic input signal 23, the diagnostic request processor 58 can initiate a self-test of the magnetic field sensor 10. The diagnostic request processor 58 can generate a diagnostic control signal 58a, and the coil driver module 24 can be coupled to receive the diagnostic control signal 58a. In response to the diagnostic control signal 58a, the coil driver circuit 24 can generate the current signal 24a.

The processing circuit 34 (also referred to herein as a signal processor 34) can include a processing module 36 having either an analog signal processor 38, a digital signal processor 40, or any combination of analog and digital processors 38, 40 that perform any combination of analog and digital processing of the composite magnetic field signal 32a. The arrow shown between the analog signal processor 38 and the digital signal processor 40 is used merely to indicate the combination of analog and digital signal processing and various couplings therebetween.

The signal processor 34 can also include a gain adjustment module 42, an offset adjustment module 44, and a temperature adjustment module 46, each coupled to the processing module 36. The gain adjustment module 42 is configured to contribute to a signal 48 received by the processing module 36, which signal 48 is configured to adjust or calibrate a gain of the processing module 36. The offset adjustment module 44 is also configured to contribute to the signal 48 received by the processing module 36, which signal 48 is also configured to adjust or calibrate a DC offset of the processing module 36. The temperature adjustment module 46 is also configured to contribute to the signal 48 received by the processing module 36, which signal 48 is configured to adjust or calibrate a gain and/or a DC offset of the processing module 36 over temperature excursions. It will be understood that that gain, offset, and temperature are but some common parameters that are compensated/adjusted, but that compensation/adjustment is not limited to those parameters only.

The processing module 36 is configured to generate the sensor signal 36a representative of the above-described measured-magnetic-field-responsive signal portion. The processing module 36 is also configured to generate at least one of the diagnostic signal 36c representative of the above-described self-test-responsive signal portion or the composite signal 36b representative of both the measured-magnetic-field-responsive signal portion and the self-test-responsive signal portion.

In some embodiments, the magnetic field sensor 10 can also include output circuits 50, for example, a sensor output formatting circuit 52, a diagnostic output formatting circuit 56, and a combining circuit 54. Operation of the sensor output

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formatting circuit 52, the diagnostic output formatting circuit 56, and the combining circuit 54 will be further understood from discussion below in conjunction with FIGS. 8-8D and 9-9E. Let it suffice here to say that the sensor output formatting circuit 52 can reformat the signal 36a representative of the measured-magnetic-field-responsive signal portion to generate a sensor output signal 52a (Sensor_Out). The diagnostic signal formatting circuit 56 can reformat the signal 36c representative of the self-test-responsive signal portion to generate a diagnostic output signal 56a (Diag_Out). The combining circuit 54 can either reformat the signal 36b representative of both the measured-magnetic-field-responsive signal portion and the self-test-responsive signal portion to generate a combined output signal 54a (Combined_Out), or it can use the signals 52a, 56a to accomplish a similar result.

The magnetic field sensor 10 can also provide an external coil drive signal 16 and an external ground 20, which can be coupled to an external conductor or coil 18. The coil 18 can be used in place of the self-test current conductor 30 to generate the above-described self-test magnetic field.

In operation, the current signal 24a can be a pulse signal, and therefore, the self-test magnetic field can be a pulsed magnetic field generated by the self-test current conductor 30 or by the external coil 18. The self-test magnetic field can physically combine with the above-described measured magnetic field, which is a field associated with that which the magnetic field sensor 10 is intended to measure. For example, the magnetic field sensor 10 can be intended to measure a magnetic field associated with a ferromagnetic or magnetic object, which generates the measured magnetic field. For another example, the magnetic field sensor 10 can be intended to measure a current flowing in a conductor (not shown), which generates the measured magnetic field.

In operation, the combination of the measured magnetic field and the self-test magnetic field is received by the magnetic field sensing element 32. The self-test magnetic field can be initiated by way of the diagnostic input signal 23, described more fully below in conjunction with FIGS. 7-7F. The self-test magnetic field can also be initiated in other ways described more fully below in conjunction with FIG. 4. The magnetic field sensing element thus generates the above described composite magnetic field signal 32a having a measured-magnetic-field-responsive signal portion, which is responsive to the measured magnetic field, and a self-test-responsive signal portion, which is responsive to the self-test magnetic field.

In some embodiments, the processing circuit 36 can operate to separate the measured-magnetic-field-responsive signal portion from the self-test-responsive signal portion to generate the sensor signal 36a representative of the magnetic field-signal portion and the diagnostic signal 36c representative of the self-test-responsive signal portion. However, in some embodiments, the processing circuit can generate the composite signal 36b representative of both the measured-magnetic-field-responsive signal portion and the self-test-responsive signal portion in addition to or in place of the signal 36c.

In operation the output circuits 50 can reformat the signals 36a-36c into at least the formats described below in conjunction with FIGS. 8A-8D, 9, 9B-9E, 10A, and 10B.

Referring now to FIG. 2, in which like elements of FIG. 1 are shown having like reference designations, a self-test current conductor 30' (where the prime symbol is indicative of one particular variation of the self-test current conductor 30 of FIG. 1) is proximate to the magnetic field sensing element 32. When a current in the direction of the arrow on the conductor 30' passes through the self-test current conductor 30',

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a self-test magnetic field 60a is generated and is received by the magnetic field sensing element 32 as a magnetic field generally perpendicular to a major surface of the magnetic field sensing element 32. Thus, this arrangement is generally suitable for most types of Hall effect elements.

The self-test magnetic field 60a can be a pulsed magnetic field generated by a pulsed current carried by the self-test current conductor 30'. The self-test magnetic field 60a physically adds to any other magnetic field (not shown), e.g., the measured magnetic field, experienced by the magnetic field sensing element 32.

Referring now to FIG. 2A, in which like elements of FIGS. 1 and 2 are shown having like reference designations, a self-test current conductor 30" is proximate to the magnetic field sensing element 32. The self-test current conductor 30" forms a single-turn loop around the magnetic field sensing element 32. When a current in the direction of the arrows on the conductor 30" passes through the self-test current conductor 30", a self-test magnetic field 60b is generated and is received by the magnetic field sensing element 32 as a magnetic field generally perpendicular to a major surface of the magnetic field sensing element 32. Thus, this arrangement is also generally suitable for most types of Hall effect elements.

It will be understood that the self-test magnetic field 60b is larger than the self-test magnetic field 60a of FIG. 2 when the self-test current is the same.

The self-test magnetic field 60b can be a pulsed magnetic field generated by a pulsed current carried by the self-test current conductor 30". The self-test magnetic field 60b physically adds to any other magnetic field (not shown), e.g., the measured magnetic field, experienced by the magnetic field sensing element 32.

Referring now to FIG. 2B, in which like elements of FIGS. 1, 2 and 2A are shown having like reference designations, a self-test current conductor 30''' is proximate to the magnetic field sensing element 32. The self-test current conductor 30''' forms a multi-turn loop or coil around the magnetic field sensing element 32. When a current in the direction of the arrows on the conductor 30''' passes through the self-test current conductor 30''', a self-test magnetic field 60c is generated and is received by the magnetic field sensing element 32 as a magnetic field generally perpendicular to a major surface of the magnetic field sensing element 32. Thus, this arrangement is also generally suitable for most types of Hall effect elements.

It will be understood that the self-test magnetic field 60c is larger than the self-test magnetic field 60a of FIG. 2 and the self-test magnetic field 60b of FIG. 2A when the self-test current is the same.

The self-test magnetic field 60c can be a pulsed magnetic field generated by a pulsed current carried by the self-test current conductor 30'''. The self-test magnetic field 60c physically adds to any other magnetic field (not shown), e.g., the measured magnetic field, experienced by the magnetic field sensing element 32.

Referring now to FIG. 2C, in which like elements of FIGS. 1, 2, 2A, and 2B are shown having like reference designations, a self-test current conductor 30'''' is proximate to the magnetic field sensing element 32. When a current in the direction of the arrow on the conductor 30'''' passes through the self-test current conductor 30''', a self-test magnetic field 60d is generated and is received by the magnetic field sensing element 32 as a magnetic field generally parallel to a major surface of the magnetic field sensing element 32. Thus, this arrangement is generally suitable for most types of magnetoresistance elements.

The self-test magnetic field **60d** can be a pulsed magnetic field generated by a pulsed current carried by the self-test current conductor **30'''**. The self-test magnetic field **60d** physically adds to any other magnetic field (not shown), e.g., the measured magnetic field, experienced by the magnetic field sensing element **32**.

Referring now to FIG. 2D, in which like elements of FIGS. 1, 2, 2A, 2B, and 2C are shown having like reference designations, a self-test current conductor **30''''** is proximate to the magnetic field sensing element **32**. The magnetic field sensing element **32** is comprised of four magnetic field sensing elements **32a-32d**. When a current in the direction of the arrow on the conductor **30''''** passes through the self-test current conductor **30''''**, a self-test magnetic field **60e** is generated and is received by the magnetic field sensing elements **32a-32d** as a magnetic field generally parallel to major surfaces of the magnetic field sensing elements **32a-32d**. Thus, this arrangement is generally suitable for most types of magnetoresistance elements.

The self-test magnetic field **60e** can be a pulsed magnetic field generated by a pulsed current carried by the self-test current conductor **30''''**. The self-test magnetic field **60e** physically adds to any other magnetic field (not shown), e.g., the measured magnetic field, experienced by the magnetic field sensing elements **32a-32d**. In some arrangements, node **62a** can be coupled to a power supply voltage, for example, Vcc, node **62d** can be coupled to a voltage reference, for example, ground, and nodes **62b**, **62c** can provide a differential output signal.

Referring now to FIG. 3, a cross section of a portion of a magnetic field sensor **70** is representative of the magnetic field sensing element **32** and self-test current conductor **30'''** of FIG. 2B. The magnetic field sensor **70** includes a magnetic field sensing element **92** supported by a substrate **82** having a surface **82a**. The magnetic field sensing element **92** may be impregnated into or diffused into and below the surface **82a** of the substrate **82**, such as is known for manufacturing of Hall effect elements. The magnetic field sensing element **92** can have a maximum response axis **96** generally perpendicular to the surface **82a** of the substrate **82**.

The magnetic field sensor **70** can include metal layers **84**, **86**, **88** separated by insulating layers **76**, **78**, **80**. Other metal and insulating layers (not shown) can be disposed between the conductive layer **76** and the metal layer **84**. An electro-magnetic shield **72** can be disposed over another insulating layer **74**.

Sections **94a-94c** are representative of a coil self-test conductor, such as the self-test conductor **30'''** of FIG. 2B and representative of the self-test conductor **30** of FIG. 1. The sections **94a-94c** can form one continuous self-test conductor, here disposed on different ones of the metal layers **84**, **86**, **88** and coupled by way of vias **90a**, **90b**. A self-test current carried by the self-test conductor **94a-94c** tends to form a self-test magnetic field along the maximum response axis **96**.

Referring now to FIG. 3A, in which like elements of FIG. 3 are shown having like reference designations, a magnetic field sensor **100** can include all of the layers of the magnetic field sensor **70** of FIG. 3 and also the magnetic field sensing element **92** of FIG. 3, but the self-test conductor **94a-94c** of FIG. 3 can be replaced by a continuous external coil self-test conductor **102**, which, in some embodiments, can be disposed upon a circuit board **104**. The external self-test conductor **102** is representative of the external self-test conductor **18** of FIG. 1. The self-test conductor **102**, shown on one metal layer of the circuit board **104**, can instead be formed from a plurality of metal layers upon the circuit board **104**. A self-test current

carried by the self-test conductor **102** tends to form a self-test magnetic field along the maximum response axis **96**.

Referring now to FIG. 3B, in which like elements of FIGS. 3 and 3A are shown having like reference designations, a magnetic field sensor **110** can include all of the layers of the magnetic field sensors **70** of FIGS. 3 and **100** of FIG. 3A, but the external self-test conductor **102** of FIG. 3A can be replaced by a continuous external coil self-test conductor **114**. Furthermore, the magnetic field sensing element **92** of FIGS. 3 and 3A can be replaced by a magnetic field sensing element **112** having a maximum response axis **116** generally parallel to the surface **82a** of the substrate **82**. The external self-test conductor **114** is representative of the external self-test conductor **18** of FIG. 1.

The magnetic field sensing element **112** may be disposed on or near the surface **82a** of the substrate **82**, such as is known for manufacturing of magnetoresistance elements. The magnetic field sensing element **92** can have a maximum response axis **116** generally parallel to the surface **82a** of the substrate **82**. A self-test current carried by the self-test conductor **114** tends to form a self-test magnetic field along the maximum response axis **116**.

Referring now to FIG. 3C, in which like elements of FIGS. 3-3B are shown having like reference designations, a magnetic field sensor **120** can include all of the layers of the magnetic field sensors **70**, **100** and **110** of FIGS. 3, 3A, and 3B, respectively, and also the magnetic field sensing element **112** of FIG. 3B, but the external self-test conductor **114** of FIG. 3B can be replaced by an internal single conductor self-test conductor **122**. The self-test conductor **122** is representative of the self-test conductor **30** of FIG. 1 and the self-test conductor **30'''** of FIG. 2C.

A self-test current carried by the self-test conductor **122** tends to form a self-test magnetic field along the maximum response axis **116**.

Referring now to FIG. 3D, in which like elements of FIGS. 3-3C are shown having like reference designations, a magnetic field sensor **130** can include all of the layers of the magnetic field sensors **70**, **100**, **110**, and **120** of FIGS. 3, 3A, 3B, and 3C, respectively, but the internal self-test conductor **122** of FIG. 3C can be replaced by an external single conductor self-test conductor **132**, which, in some embodiments, can be disposed upon a circuit board **134**. The self-test conductor **132** is representative of the external self-test conductor **18** of FIG. 1.

A self-test current carried by the self-test conductor **132** tends to form a self-test magnetic field along the maximum response axis **116**.

While FIGS. 3-3D show various alternative embodiments associated with the magnetic field sensing element **32** and self-test current conductors **30**, **18** or FIG. 1, it will be recognized that there are many other possible configurations, including, but not limited to, combinations of the configurations shown.

While FIGS. 3-3D are representative of portions of magnetic field sensors **70**, **100**, **110**, **120**, **130**, it should be understood that the magnetic field sensing element **32** and self-test current conductor **30** of FIG. 1 can be disposed on the same substrate as other portions of the magnetic field sensor **10** of FIG. 1, or, in other embodiments on a second different substrate from the other portions of the magnetic field sensor **10** of FIG. 1.

Referring now to FIG. 3E, a magnetic field sensor **144**, here encased in a package **142**, can be the same as or similar to the magnetic field sensor **10** of FIG. 1. The magnetic field sensor **144** can be coupled to a lead frame having leads **146**. The leads **146** can be electrically coupled to a circuit board **150**.

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The magnetic field sensor **144** can be responsive to a magnetic field **148** perpendicular to a major surface of the magnetic field sensor **144**, such as may be generated by proximity of a magnetic field source **140**, for example, a hard ferromagnetic object.

Referring now to FIG. 3F, a magnetic field sensor **156**, here encased in a package **154**, can be the same as or similar to the magnetic field sensor **10** of FIG. 1. The magnetic field sensor **156** can be coupled to a lead frame having leads, of which leads **160a**, **160b** are representative. The leads, e.g., **160a**, **160b**, can be electrically coupled to a circuit board **150**. The magnetic field sensor **156** can be responsive to a magnetic field **164** parallel to a major surface of the magnetic field sensor **156**, such as may be generated by proximity of a magnetic field source **152**, for example, a hard ferromagnetic object.

Also shown, in some alternate embodiments, the leads can be coupled with a measured conductor **158**, which can be formed as a part of the lead frame of which the leads **160a**, **160b** are another part. A measured current carried by the measured conductor **158** tends to form a magnetic field **162** going into or out of the page, depending upon a direction of the current carried by the measured conductor **158**. For these arrangements, the magnetic field sensor **156** can be a current sensor and the magnetic field sensor **156** can instead be responsive to the magnetic field **162** perpendicular to the major surface of the magnetic field sensor **156** (i.e., to the current) rather than to the magnetic field **164**.

Referring now to FIG. 3G, a magnetic field sensor **170**, here encased in a package **168**, can be the same as or similar to the magnetic field sensor **10** of FIG. 1. The magnetic field sensor **170** can be coupled to a lead frame having leads, of which a lead **174** is representative. The leads, e.g., **174**, can be electrically coupled to a circuit board **176**. The magnetic field sensor **170** can be responsive to a magnetic field generated by proximity of a magnetic field source **172** within the package **168**. For example, the magnetic field source **172** can be a measured current conductor similar to the measured current conductor **158** of FIG. 3F.

Referring now to FIG. 4, a diagnostic request processor **190** can be the same as or similar to the diagnostic request processor **58** of FIG. 1. The diagnostic request processor **190** can be coupled to receive a diagnostic input signal **192**, which can be the same as or similar to the diagnostic input signal **23** of FIG. 1. The diagnostic request processor **190** can include a diagnostic input decoder **204** to receive and to decode the diagnostic input signal **192**. The diagnostic input decoder **204** can generate a decoded diagnostic signal **204a**.

The diagnostic request processor **190** can also include a pulse generator **198** coupled to receive the decoded diagnostic signal **204a** and configured to generate a diagnostic control signal **198a** having pulses in response to the decoded diagnostic signal **204a**. The diagnostic control signal **198a** can be the same as or similar to the diagnostic control signal **58a** of FIG. 1.

The diagnostic request processor **190** can also include a clock generator **194** configured to generate a periodic clock signal **194a**. The diagnostic request processor **190** can also include an internal diagnostic clock generator **196** coupled to receive the clock signal **194a** and configured to generate a periodic diagnostic clock signal **196a**.

The pulse generator **198** can be coupled to receive the diagnostic clock signal **196a** and can be configured to generate the diagnostic control signal **198a** having pulses synchronized with the diagnostic clock signal **196a**.

Thus, there can be at least two ways to control the pulse generator **198** and associated diagnostics events, i.e., pulses

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within the diagnostic input signal **198a**. As described above, the pulse generator **198** can be responsive to the diagnostic input signal **192**. Alternatively, the pulse generator **198** can be responsive to the control signal **196a** instead of, or in addition to, the diagnostic input signal **192**. When responsive to the control signal **196a**, the pulse generator **198** can generate pulses at periodic time intervals, or groups of pulses at periodic time intervals.

The diagnostic request processor **190** can also include a power on circuit **202** coupled to generate power on signal **202a** having a first state for a predetermined period of time after the magnetic field sensor, e.g., the magnetic field sensor **10** of FIG. 1, is first powered on, followed by a second different state. The pulse generator **196** can be coupled to receive the power on signal **202a** and can be further responsive to the power on signal **202a** such that the pulse generator **198** also generates pulses in the diagnostic control signal **198a** in response to the power on signal **202a**.

In some embodiments, the diagnostic clock signal **196a** has a frequency in the range of about ten Hz to one hundred Hz. However, the diagnostic clock signal **196a** can also have a frequency higher than one hundred Hz (e.g., one thousand Hz) or lower than ten Hz (e.g., one Hz) or anywhere in between ten Hz and one hundred Hz.

In some embodiments, the pulse generator **198** generates pulses having a period between about one μ s and ten μ s in the diagnostic control signal **198a**. However, the pulse generator **198** can also generate pulses having a period greater than ten μ s (e.g., one hundred μ s) or less than one μ s (e.g., 0.1 μ s) or anywhere in between one μ s and ten μ s.

The diagnostic control signal **198a** can be received by a coil driver circuit **200**, for example, a current source, which can be the same as or similar to the coil driver circuit **24** of FIG. 1. The coil driver circuit **200** can generate a self-test current signal **200a**, which is received by a self-test current conductor the same as or similar to the self-test current conductor **30** of FIG. 1 or the external coil **18** of FIG. 1.

Referring now to FIG. 5, a magnetic field sensor **210** can be the same as or similar to the magnetic field sensor **10** of FIG. 1. The magnetic field sensor **210** can include a current source **216** coupled to receive a supply voltage signal **212** and configured to generate a self-test current signal **218**. The current source **216** can be the same as or similar to the coil driver **24** of FIG. 1.

The magnetic field sensor **210** can also include a self-test current conductor **224** coupled to receive and carry the self-test current signal **218**. While the self-test current conductor **224** is shown to be a coil, from FIGS. 2-2D, it will be understood that the self-test current conductor **224** can have one of a variety of arrangements.

The magnetic field sensor **210** can also include a magnetic field sensing element **226** proximate to the self-test current conductor **224** such that the magnetic field sensing element **226** can receive a self-test magnetic field generated by the current **218** carried by the self-test current conductor **224**. The magnetic field sensing element **226** can also receive a measured magnetic field associated with a magnetic field generator (not shown) that the magnetic field sensor **210** is intended to measure. Thus, the magnetic field sensor is configured to generate a differential composite magnetic field signal **226a**, **226b** comprising a measured-magnetic-field-responsive signal portion and a self-test-responsive signal portion.

The magnetic field sensor **210** can also include an amplifier **228** coupled to receive the composite magnetic field signal **226a**, **226b** and configured to generate an amplified signal **228a** representative of the composite magnetic field signal **226a**, **226b**.

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The magnetic field sensor **210** can also include a low pass filter **230** and a high pass filter **248**, each coupled to receive the amplified signal **228a**. The low pass filter **230** is configured to generate a filtered signal **230a** and the high pass filter **248** is configured to generate a filtered signal **248a**.

A comparator **240** can be coupled to receive the filtered signal **230a**. The comparator **240** can have hysteresis or other circuit techniques to result in two thresholds **242**, a magnetic field operate point (BOP) and a magnetic field release point (BRP). The BOP and BRP thresholds **242**, in some embodiments, can be separated by a voltage equivalent to about five Gauss received by the magnetic field sensing element **226**. In other embodiments, the BOP and BRP thresholds **242** can be separated by a voltage equivalent to about fifty Gauss received by the magnetic field sensing element **226**. However, the BOP and BRP thresholds **242** can be separated by a voltage equivalent to a magnetic field anywhere between about five and fifty Gauss. The BOP and BRP thresholds **242** can also be separated by a voltage equivalent to a magnetic field smaller than five Gauss or larger than fifty Gauss. The comparator **240** is configured to generate a two state comparison signal **240a**.

A comparator **250** can be coupled to receive the filtered signal **248a**. The comparator **250** can have hysteresis or other circuit techniques to result in two thresholds, which can be relatively closely spaced about a diagnostic threshold voltage (TH_Diag) **252**. In some embodiments, the hysteresis associated with the diagnostic threshold voltage **252** is about fifty millivolts. The comparator **250** is configured to generate a two state comparison signal **250a**.

The magnetic field sensor **210** can also include a sensor output formatting circuit (SOFC) **244** coupled to receive the comparison signal **240a** and configured to generate a sensor non-linear output signal **244a**. The SOFC **244** can be the same as or similar to the sensor output formatting circuit **52** of FIG. 1.

The magnetic field sensor **210** can also include a diagnostic output formatting circuit (DOFC) **254** coupled to receive the comparison signal **250a** and configured to generate a diagnostic output signal **254a**. The DOFC **254** can be the same as or similar to the diagnostic output formatting circuit **56** of FIG. 1.

The magnetic field sensor **210** can also include a combining circuit **256** coupled to receive the sensor non-linear output signal **244a**, coupled to receive the diagnostic output signal **254a**, and configured to generate a combined output signal **256a**. The combining circuit **256** can be the same as or similar to the combining circuit **54** of FIG. 1.

The magnetic field sensor **210** can also include another SOFC **246** coupled to receive the filtered signal **230a** and configured to generate a sensor linear output signal **246a**. The SOFC **246** can be the same as or similar to the sensor output formatting circuit **52** of FIG. 1.

The magnetic field sensor **210** can also include a diagnostic request processor **260** coupled to receive a diagnostic input signal **258** and configured to generate a diagnostic control signal **260a**. The diagnostic request processor **260** can be the same as or similar to the diagnostic request processor **58** or FIG. 1 or the diagnostic request processor **190** of FIG. 4. Operation of the diagnostic request processor **260** can be as is described above in conjunction with FIG. 4 and is further described below in conjunction with FIGS. 7-7F.

In operation, upon activation of the diagnostic control signal **260a**, the current source **216** can generate one or more current pulses **218**, which are carried by the self-test conductor **224** resulting in a self-test magnetic field received by the magnetic field sensing element **226**. It will be understood that

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the self-test magnetic field, and therefore, the self-test-responsive signal portion of the composite magnetic field signal **226a**, **226b**, can have a frequency content that is generally above a frequency content of a measured magnetic field that the magnetic field sensor **210** is intended to measure. Therefore, the filtered signal **248a** can be comprised predominantly of the self-test-responsive signal portion, i.e., pulses, and the filtered signal **230a** can be comprised predominantly of the measured-magnetic-field-responsive signal portion. Therefore, by way of the filters **230**, **248**, the composite magnetic field signal **226a**, **226b** is split into its two components, the self-test-responsive signal portion and the measured-magnetic-field-responsive signal portion.

In one particular embodiment, the low pass filter **230** has a break frequency of about two hundred kHz and the high pass filter **248** has a break frequency above about two hundred kHz, such that the signal **248a** tends to represent the self-test-responsive signal portion of the composite magnetic field signal **226a**, **226b**. Accordingly, in some embodiments, the measured magnetic field can have a frequency below about two hundred kHz.

It will be understood that the comparator **250** and the diagnostic threshold **252** can assure that the pulses in the filtered signal **248a** are of proper and sufficient magnitude to be indicative of proper operation of the magnetic field sensing element **226**, amplifier **228**, and filter **248**. In operation, the comparator **250** generates the two-state comparison signal **250a**, i.e., pulses, only when the pulses in the filtered signal **248a** are proper. Pulses of the comparison signal **250a** can be reformatted into any format by the DOFC **254** to generate the diagnostic output signal **254a**. Exemplary formats of the diagnostic output signal **254a** are described below in conjunction with FIGS. 8A-8D.

As described above, the filtered signal **230a** is predominantly comprised of the measured-magnetic-field-responsive signal portion. The SOFC **246** can reformat the filtered signal **230a** into any format to generate the sensor linear output signal **246a**. In one particular embodiment, the SOFC **246** merely passes the filtered signal **230a** through the SOFC **246**, in which case no reformatting occurs.

The comparison signal **240a** can be indicative of the magnetic field sensor **210** that operates as a magnetic switch. For example, when the magnetic field sensing element **226** is close to a measured magnetic object, resulting in a magnetic field at the magnetic field sensing element **226** greater than an operating point, the comparison signal **240a** has a first state, and when the magnetic field sensing element **226** is not close to the measured magnetic object, resulting in a magnetic field at the magnetic field sensing element **226** less than a release point, the comparison signal **240a** has a second different state. The SOFC **244** can reformat the comparison signal **240a** into any format to generate the sensor non-linear output **244a**. In one particular embodiment, the SOFC **244** merely passes the comparison signal **240a** through the SOFC **244**, in which case no reformatting occurs.

While many of the blocks of the magnetic field sensor **210** are shown to be analog blocks, it should be appreciated that similar functions can be performed digitally.

Referring now to FIG. 5A, in which like elements of FIG. 5 are shown having like reference designations, a magnetic field sensor **300** includes all of the components of the magnetic field sensor **210** of FIG. 5. In addition, the magnetic field sensor **300** includes an inverter **302** configured to generate an inverted diagnostic control signal **302a**. The magnetic field sensor **300** also includes an AND gate **304** coupled to receive the comparison signal **250a**, coupled to receive the diagnostic control signal **260a**, and configured to generate a diagnostic

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comparison signal **304a**. The magnetic field sensor **300** also includes a switch **222**, which can be a FET, coupled across the self-test current conductor **224** and controlled by the inverted diagnostic control signal **302a**. The magnetic field sensor **300** also includes a logic circuit **306** configured to generate a sensor non-linear threshold (TH_SONL) **314** received by the amplifier **240** in place of the BOP/BRP threshold **242** of FIG. 5. Each of these added elements improves operation of the magnetic field sensor **210** of FIG. 5 in ways further described below.

The logic circuit **306** can include an AND gate **308** coupled to receive the diagnostic comparison signal **304a**, coupled to receive the non-linear sensor comparison signal **240a**, and configured to generate a logic signal **308a**. The logic signal **308a** can be received at a set node of a set/reset flip-flop **310**. The set/reset flip-flop **310** can also be coupled to receive the inverted diagnostic control signal **302a** at a reset node. The set/reset flip-flop **310** can be configured to generate a control signal **310a** received by a p-channel FET **312** acting as a switch to a power supply, Vcc.

The logic circuit **306** can include an inverter **316** coupled to receive the non-linear sensor comparison signal **240a'** and configured to generate an inverted signal **316a**. The logic circuit **306** can also include another AND gate **318** coupled to receive the diagnostic comparison signal **304a**, coupled to receive the inverted signal **316a**, and configured to generate a logic signal **318a**. The logic signal **318a** can be received at a set node of another set/reset flip-flop **320**. The set/reset flip-flop **320** can also be coupled to receive the inverted diagnostic control signal **302a** at a reset node. The set/reset flip-flop **320** can be configured to generate a control signal **320a** received by an n-channel FET **322** acting as a switch to ground. A source of the FET **312** can be coupled to a drain of the FET **322**, forming a junction node. The BOP/BRP thresholds can also be received at the junction node. At the junction node, the sensor output non-linear threshold signal **314** is generated.

With this arrangement, it should be understood that at some times, the sensor output non-linear threshold **314** is equal to BOP, at other times it is equal to BRP, at other times it is equal to Vcc, and at other times it is equal to ground.

Referring briefly to FIG. 5, it should be understood that the self-test current **218** and resulting self-test-responsive signal portion of the composite magnetic field signal **226a**, **226b** does not pass through the comparator **240** or the SOFC **244**. Thus, the comparator **240** and SOFC **244** are essentially excluded from the self-test.

Referring again to FIG. 5A, the logic circuit **306** provides that the comparator **240** and SOFC are included in the self-test in the following way. Whenever a diagnostic pulse occurs in the self-test current signal **218**, the non-linear sensor output threshold **314** is pulled either to Vcc or to ground. At other times, the non-linear sensor output threshold **314** behaves as in FIG. 5, wherein the non-linear sensor output threshold **314** is either at a BOP or BRP voltage value. Thus, the sensor non-linear output signal **244a'** (where the prime symbol is representative of a difference from the signal **244a** of FIG. 5) makes state transitions not only responsive to a measured magnetic object near to or far from the magnetic field sensing element **226**, but also makes transitions when self-test pulses occur. It should be recognized that the same result may not be achieved by merely removing the filter **230**, for example, in the case where the measured magnetic field is much greater than the self-test magnetic field, wherein the comparator **240** would not switch in the presence of the self-test-responsive signal portion. This function is further described in conjunction with FIGS. 10-10B.

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The addition of the AND gate **304** having an input node coupled to receive the diagnostic control signal **260a** results in removal of a possibility that any extraneous spikes or noise pulses in the comparison signal **250a** could pass through to the diagnostic output signal **254a** when no self-test current pulse **218** is ongoing. Such spikes could result from external magnetic field noise or pulses experienced by the magnetic field sensor **300**.

The switch **222** also provides improved function. The switch **222** is only opened when a self-test current pulse **218** is ongoing. The switch is closed at other times. Thus, any external noise or magnetic fields experienced by the magnetic field sensor **300** will not be picked up by the self-test conductor at times when no self-test current pulses **218** are occurring.

Basic operation of the current sensor **300** is described above in conjunction with FIG. 5. The sensor non-linear output signal **244a'** is described below in conjunction with FIG. 10B.

Referring now to FIG. 5B, in which like elements of FIGS. 1, 5, and 5A are shown having like reference designations, output circuits **350** can be included as part of the magnetic field sensors **210**, **300** of FIGS. 5 and 5A or any other magnetic field sensors shown or described herein. Output circuits **350** can include resistors **352a-352c** coupled to a power supply, Vdd, and coupled to a respective drain of respective FETs **354a-354c**. FET **354a** can be coupled to receive the sensor non-linear output signal **244a** at a gate node and configured to generate an inverted sensor non-linear output signal **356**. FET **354b** can be coupled to receive the diagnostic output signal **254a** at a gate node and configured to generate an inverted diagnostic output signal **358**. FET **354c** can be coupled to receive the combined output signal **256a** at a gate node and configured to generate an inverted combined output signal **360**.

In some embodiments, the FETs **354a-354c** are within an integrated magnetic field sensor, and the resistors **352a-352c** and the power supply, Vdd, are outside of the integrated magnetic field sensor. However, in other embodiments, both the FETs **354a-354c** and the resistors **352a-352c** are within the integrated current sensor. In still other embodiments, other output circuit arrangements can be used, for example, using bipolar transistors or using a push pull configuration.

Referring now to FIG. 6, in which like elements of FIGS. 1, 5, and 5A are shown having like reference designations, a magnetic field sensor **370** is similar to the magnetic field sensor **210** of FIG. 5, however, the magnetic field sensor **370** includes a transparent latch **372** coupled between the comparator **240** and the SOFC **244**, coupled to receive the comparison signal **240a** at an input port and configured to generate a latched signal **372a** at an output port, which is received by the SOFC **244**. The transparent latch **372** is also coupled to receive the inverted diagnostic control signal **302a** at an enable port.

The magnetic field sensor **370** also includes a track-and-hold circuit **374** coupled to receive the amplified signal **228a** and configured to generate a tracking signal **374a**. The track-and-hold circuit **374** is also coupled to receive the diagnostic control signal **260a** at a control node such that the track-and-hold circuit holds whenever a current pulse appears in the self-test current signal **218** and tracks otherwise. The magnetic field sensor **370** also includes a differencing circuit **376** coupled to receive the amplified signal **228a**, coupled to receive the tracking signal **374a**, and configured to generate a difference signal **376a** received by the comparator **250** in place of the filtered signal **248a** of FIG. 5. The magnetic field sensor **370** also includes the AND gate **304** of FIG. 5A coupled to receive a comparison signal **250a'**, similar to the

comparison signal **250a** of FIGS. **5** and **5A**, where the prime symbol is representative of a similar signal. The magnetic field sensor **370** can also include an optional low pass filter **378** coupled to receive the amplified signal **228a** and configured to generate a filtered signal **378a**, which can be the same as or similar to the filtered signal **230a** of FIG. **5**.

In operation, the transparent latch **372** is transparent only when the self-test current signal **218** does not contain a current pulse. Therefore, the latched signal **372a**, which is intended to be representative of only the measured-magnetic-field-responsive signal portion of the composite magnetic field signal **226a**, **226b** is less likely to contain spurious transitions due to the current pulses.

In operation, the tracking signal **374a** contains predominantly the measured-magnetic-field-responsive signal portion of the amplified signal **228a**, since the track-and-hold circuit holds during the self-test-responsive signal portion of the amplified signal **228a**. Thus, the tracking signal **374a** is similar to the filtered signal **378a**, which is the same as or similar to the filtered signal **230a** of FIGS. **5** and **5A**. The SOFC **246'** can thus receive either the tracking signal **374a** or the filtered signal **378a** to generate the sensor linear output signal **246a'**.

General operation of the magnetic field sensor **370** is similar to that described above in conjunction with FIGS. **5** and **5A**, and thus, is not described further.

Referring to FIGS. **7-7F**, graphs **400**, **420**, **430**, **440**, **450**, **460**, and **470** have vertical axes with scales in arbitrary units of volts and horizontal axes with scales in arbitrary units of time.

The graph **400** includes a sensor non-linear output signal **402** and a sensor linear output signal **408**, which can be the same as or similar to the sensor non-linear output signal **244a** and the sensor linear output signal **246a** of FIG. **5**, respectively. The sensor non-linear output signal **402** includes high states, for example, high states **404a**, **404b** and low states, for example, a low state **406**.

The sensor linear output signal **408** is shown here as a triangle signal, but can be any linear signal. The sensor linear output signal **408** includes sections with positive slopes, for example, sections **410a**, **410b**, and sections with negative slopes, for example, a section **412**.

The graph **420** includes an exemplary diagnostic control signal **422**, which can be the same as or similar to the diagnostic control signal **260a** of FIGS. **5**, **5A**, and **6**. The graph **420** can also be representative of a diagnostic output signal, which can be the same as or similar to the diagnostic output signal **254a**, **254a'** of FIGS. **5**, **5A**, and **6** and the diagnostic control signal **198a** of FIG. **4**. It should be understood that the graph **420** can also be representative of current pulses in the self-test current signal **218** of FIGS. **5**, **5A**, and **6**.

The signal **422** can include pulses, of which a pulse **424** is but one example. While the signal **422** is shown to include five pulses, other such signals **422** can include more than five or fewer than five pulses.

The graph **430** includes an exemplary diagnostic input signal **432**, which can be the same as or similar to the diagnostic input signal **258** of FIGS. **5**, **5A**, and **6**, the diagnostic input signal **23** of FIG. **1**, and the diagnostic input signal **192** of FIG. **4**. The exemplary diagnostic input signal **432** can include pulses, of which a pulse **434** is but one example. Each pulse of the diagnostic input signal **432** can result in one corresponding pulse of the diagnostic control signal **422** and one corresponding pulse of the diagnostic output signal **422**.

While the signal **432** is shown to include five pulses, other such signals **432** can include more than five or fewer than five pulses.

The graph **440** includes another exemplary diagnostic input signal **442**, which can be the same as or similar to the diagnostic input signal **258** of FIGS. **5**, **5A**, and **6**, the diagnostic input signal **23** of FIG. **1**, and the diagnostic input signal **192** of FIG. **4**. The diagnostic input signal **442** can have one pulse **444**. Each pulse of the diagnostic input signal **442** can result in a plurality of pulses of the diagnostic control signal **422** and a corresponding plurality of pulses of the diagnostic output signal **422**.

The graph **450** includes yet another exemplary diagnostic input signal **452**, which can be the same as or similar to the diagnostic input signal **258** of FIGS. **5**, **5A**, and **6**, the diagnostic input signal **23** of FIG. **1**, and the diagnostic input signal **192** of FIG. **4**. The diagnostic input signal **452** can have a high state **454**, a low state **456**, and an edge **458**. The high state **454** of the diagnostic input signal **452** can result in a plurality of pulses of the diagnostic control signal **422** and a corresponding plurality of pulses of the diagnostic output signal **422**.

The graph **460** includes yet another exemplary diagnostic input signal **462**, which can be the same as or similar to the diagnostic input signal **258** of FIGS. **5**, **5A**, and **6**, the diagnostic input signal **23** of FIG. **1**, and the diagnostic input signal **192** of FIG. **4**. The diagnostic input signal **462** can have pulses, e.g., a pulse **464**, with a first duty cycle, and pulses, e.g., a pulse **466**, with a second different duty cycle. Rising edges of the pulses **464** having the first duty cycle, and including an edge **466**, can each result in one corresponding pulse of the diagnostic control signal **422** and one corresponding pulse of the diagnostic output signal **422**. The pulses **466** having the second different duty cycle result in no pulse in the diagnostic control signal **422** or in the diagnostic output signal **422**.

The graph **470**, which has a time scale expanded from that of FIGS. **7-7F** includes yet another exemplary diagnostic input signal **478**, which can be the same as or similar to the diagnostic input signal **258** of FIGS. **5**, **5A**, and **6**, the diagnostic input signal **23** of FIG. **1**, and the diagnostic input signal **192** of FIG. **4**. The diagnostic input signal **478** can have a digital chip address **472**, a digital register address **474**, and digital register data **476**. The diagnostic input signal **478** can result in a plurality of pulses of the diagnostic control signal **422** and a corresponding plurality of pulses of the diagnostic output signal **422**.

The diagnostic input signal **478** can be in one of a variety of formats or protocols, for example, a custom protocol or a conventional protocol, for example, I2C, SENT, BiSS, LIN, or CAN.

It should be understood that each one of the diagnostic input signals **432**, **442**, **452**, **462**, and **478** can be decoded by the diagnostic input decoder **204** of FIG. **4** to result in the diagnostic output/diagnostic control signal **422**.

It should be recognized that FIGS. **7B-7F** show only a few exemplary types of diagnostic input signals that may be used. Many other types of diagnostic input signals can also be used.

Referring now to FIGS. **8-8D**, graphs **480**, **490**, **500**, **510**, and **520** have vertical axes with scales in arbitrary units of volts and horizontal axes with scales in arbitrary units of time.

The graph **480** includes an exemplary diagnostic input signal **482**, which can be the same as or similar to the diagnostic input signal **258** of FIGS. **5**, **5A**, and **6**, the diagnostic input signal **23** of FIG. **1**, the diagnostic input signal **192** of FIG. **4**, and the diagnostic input signal **432** of FIG. **7B**. The exemplary diagnostic input signal **482** can include pulses, of which a pulse **484** is but one example.

The graph **490** includes an exemplary diagnostic control signal **492**, which can be the same as or similar to the diagnostic control signal **260a** of FIGS. **5**, **5A**, and **6**, and the

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diagnostic control signal 422 of FIG. 7A. The graph 490 can also be representative of a diagnostic output signal, which can be the same as or similar to the diagnostic output signal 254a, 254a' of FIGS. 5, 5A, and 6, the diagnostic output signal 198a of FIG. 4, and the diagnostic output signal 422 of FIG. 7A. It should be understood that the graph 490 can also be representative of current pulses in the self-test current signal 218 of FIGS. 5, 5A, and 6.

The signal 492 can include pulses, of which a pulse 494 is but one example. While the signal 492 is shown to include five pulses, other such signals 492 can include more than five or fewer than five pulses.

Each pulse of the diagnostic input signal 482 can result in one corresponding pulse of the diagnostic control signal 492 and one corresponding pulse of the diagnostic output signal 492. The pulses 494 of the diagnostic output signal 492 are indicative of a self-test that is passing.

While the signal 492 is shown to include five pulses, other such signals 492 can include more than five or fewer than five pulses.

The graph 500 includes yet another exemplary diagnostic output signal 502, which can be the same as or similar to the diagnostic output signal 254a, 254a' of FIGS. 5, 5A, and 6, and the diagnostic output signal 422 of FIG. 7A. The diagnostic output signal 502 can have a high state 504, a low state 506, and an edge 508. The high state 504 of the diagnostic output signal 502 can result from a plurality of pulses 494 of the diagnostic control signal 492 or from any of the diagnostic input signals of FIGS. 7B-7F. The high state 504 of the diagnostic output signal 502 can be indicative of a self-test that is passing.

The graph 510 includes yet another exemplary diagnostic output signal 512, which can be the same as or similar to the diagnostic output signal 254a, 254a' of FIGS. 5, 5A, and 6, and the diagnostic output signal 422 of FIG. 7A. The diagnostic output signal 512 can have pulses, e.g., a pulse 514, with a first duty cycle, and pulses, e.g., a pulse 516, with a second different duty cycle. The pulses 514 having the first duty cycle and an edge 518 can each result from one corresponding pulse of the diagnostic control signal 492 or from any of the diagnostic input signals of FIGS. 7B-7F. The pulses 514 having the first duty cycle can be indicative of a self-test that is passing.

The graph 520, which has a time scale expanded from that of FIGS. 8-8C includes yet another exemplary diagnostic output signal 528, which can be the same as or similar to the diagnostic output signal 254a, 254a' of FIGS. 5, 5A, and 6, and the diagnostic output signal 422 of FIG. 7A. The diagnostic output signal 528 can have a digital chip address 522, a digital register address 524, and digital register data 526. The diagnostic output signal 522 can result from a plurality of pulses of the diagnostic control signal 492 or from any of the diagnostic input signals of FIGS. 7B-7F. Particular digital register data 526 can be indicative of a self-test that is passing.

The diagnostic output signal 528 can be in one of a variety of formats or protocols, for example, a custom protocol or a conventional protocol, for example, I2C SENT, BiSS, LIN, or CAN.

It should be recognized that FIGS. 8A-8D show only a few exemplary types of diagnostic output signals that may be generated. Many other types of diagnostic output signals can also be generated.

Referring now to FIGS. 9-9E, graphs 530, 550, 560, 570, 580, and 590 have vertical axes with scales in arbitrary units of volts and horizontal axes with scales in arbitrary units of time.

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The graph 530, like the graph 400 of FIG. 7, includes a sensor non-linear output signal 532 and sensor linear output signal 538, which can be the same as or similar to the sensor non-linear output signal 244a and the sensor linear output signal 246a of FIG. 5, respectively. The sensor non-linear output signal 532 includes high states, for example, high states 534a, 534b, and low states, for example, a low state 536.

The sensor linear output signal 538 is shown here as a triangle signal, but can be any linear signal. The sensor linear output signal 538 includes sections with positive slopes, for example, sections 540a, 540b, and sections with negative slopes, for example, a section 542.

The graph 550, like the graph 430 of FIG. 7B and the graph 480 of FIG. 8, includes an exemplary diagnostic input signal 552, which can be the same as or similar to the diagnostic input signal 258 of FIGS. 5, 5A, and 6, the diagnostic input signal 23 of FIG. 1, and the diagnostic input signal 192 of FIG. 4. The exemplary diagnostic input signal 552 can include pulses, of which a pulse 554 is but one example.

The graph 560 includes an exemplary combined output signal 562, which can be the same as or similar to the combined output signal 256a, 256a' of FIGS. 5, 5A, and 6, and the combined output signal 54a of FIG. 1. The combined output signal 562 can include pulse groups, e.g., pulse groups 564, 566, combined with the sensor non-linear output signal 532 of FIG. 9, here shown as a dark line. The pulse groups, e.g., pulse groups 564, 566, can be indicative of a self-test that is passing.

The graph 570 includes another exemplary combined output signal 572, which can be the same as or similar to the combined output signal 256a, 256a' of FIGS. 5, 5A, and 6, and the combined output signal 54a of FIG. 1. The combined output signal 572 can include small pulses, e.g., small pulses 574, 576, combined with the sensor non-linear output signal 532 of FIG. 9, here shown as a dark line. The small pulses, e.g., the small pulses 574, 576, can be indicative of a self-test that is passing.

The graph 580 includes yet another exemplary combined output signal 582, which can be the same as or similar to the combined output signal 256a, 256a' of FIGS. 5, 5A, and 6, and the combined output signal 54a of FIG. 1. The combined output signal 582 can include pulses, e.g., pulses 584, 586, combined with the sensor non-linear output signal 532 of FIG. 9, here shown as a dark line. The pulses, e.g., the pulses 584, 586, can be indicative of a self-test that is passing.

The graph 590 includes yet another exemplary combined output signal 592, which can be the same as or similar to the combined output signal 256a, 256a' of FIGS. 5, 5A, and 6, and the combined output signal 54a of FIG. 1. The combined output signal 592 can include small pulses, e.g., pulses 594, 596, combined with the sensor linear output signal 538 of FIG. 9, here shown as a dark line. The pulses, e.g., the pulses 594, 596, can be indicative of a self-test that is passing. Digitally encoded versions of all of the above output signals are also possible.

Referring now to FIGS. 10-10B, graphs 600, 610, and 620 have vertical axes with scales in arbitrary units of volts and horizontal axes with scales in arbitrary units of time.

The graph 600, like the graph 420 of FIG. 7A and the graph 490 of FIG. 8A, includes an exemplary diagnostic control signal 602, which can be the same as or similar to the diagnostic control signal 260a of FIGS. 5, 5A, and 6, and the diagnostic control signal 198a of FIG. 4. The graph 600 can also be representative of a diagnostic output signal, which can be the same as or similar to the diagnostic output signal 254a, 254a' of FIGS. 5, 5A, and 6. It should be understood that the

graph 600 can also be representative of current pulses in the self-test current signal 218 of FIGS. 5, 5A, and 6.

The signal 602 can include pulses, of which a pulse 604 is but one example. While the signal 602 is shown to include five pulses, other such signals 422 can include more than five or fewer than five pulses.

The graph 610 includes a sensor non-linear comparison signal 612, which can be the same as or similar to the sensor non-linear comparison signal 240a' of FIG. 5A. The sensor non-linear comparison signal 612 includes high states, for example, high states 614a, 614b, and low states, for example, a low state 616.

The graph 620 includes an exemplary sensor non-linear output signal 622, which can be the same as or similar to the sensor non-linear output signal 244a' of FIG. 5A. The sensor non-linear output signal 622 is representative of the function of the logic circuit 306 of FIG. 5A. The sensor non-linear output signal 622 can include pulses, e.g., pulses 624, 626, combined with the sensor non-linear comparison signal 612 of FIG. 10A, here shown as a dark line. The pulses, e.g., the pulses 624, 626, can be indicative of a self-test that is passing, namely, a properly functioning comparator 240 and SOFC 244 of FIG. 5A.

Referring now to FIG. 11, an exemplary electromagnetic shield 800 can be the same as or similar to the electromagnetic shield 72 of FIG. 3. The electromagnetic shield 800 is placed generally over a magnetic field sensing element 816, which can be the same as or similar to the magnetic field sensing element 92 of FIG. 3. The electromagnetic shield 800 includes a first portion 802 and a second portion 804 separated by a slit 806. The first portion 802 and the second portion 804 are coupled with a conductive region 808. A bonding pad 810 allows the electromagnetic shield 800 to be coupled to a DC voltage, for example, to a ground voltage.

The electromagnetic shield 800 can be formed from a metal layer during manufacture of a magnetic field sensor, for example, the magnetic field sensor 70 of FIG. 3. The metal layer can be comprised of a variety of materials, for example, aluminum, copper, gold, titanium, tungsten, chromium, or nickel.

It should be understood that an electromagnetic shield is not the same as a magnetic shield. An electromagnetic shield is intended to block electromagnetic fields. A magnetic shield is intended to block magnetic fields.

In the presence of an AC magnetic field (e.g., a magnetic field surrounding a current carrying conductor), it will be understood that AC eddy currents 812, 814 can be induced in the electromagnetic shield 800. The eddy currents 812, 814 form into closed loops as shown. The closed loop eddy currents 812, 814 tend to result in a smaller magnetic field in proximity to the electromagnetic shield 800 than the magnetic field that induced the eddy currents 812, 814. Therefore, if the electromagnetic shield 800 were placed near a magnetic field sensing element, for example, the magnetic field sensing element 92 of FIG. 3, the magnetic field sensing element 92 experiences a smaller magnetic field than it would otherwise experience, resulting in a less sensitive magnetic field sensor, which is generally undesirable. Furthermore, if the magnetic field associated with the eddy current is not uniform or symmetrical about the magnetic field sensing element 92, the magnetic field sensing element 92 might also generate an undesirable offset voltage.

The slit 806 tends to reduce a size (i.e., a diameter or path length) of the closed loops in which the eddy currents 812, 814 travel. It will be understood that the reduced size of the closed loops in which the eddy currents 812, 814 travel results in smaller eddy currents 812, 814 and a smaller local effect on

the AC magnetic field that induced the eddy current. Therefore, the sensitivity of a magnetic field sensor on which the magnetic field sensing element 816 and the electromagnetic shield 800 are used is less affected by the smaller eddy currents.

Furthermore, by placing the shield 800 in relation to the magnetic field sensing element 816 as shown, so that the slit 806 passes over the magnetic field sensing element 816, it will be understood that the magnetic field associated with any one of the eddy currents 812, 814 tends to form magnetic fields passing through the magnetic field sensing element 816 in two directions, canceling over at least a portion of the area of the magnetic field sensing element 816.

Referring now to FIG. 12, another exemplary electromagnetic shield 850 can be the same as or similar to the electromagnetic shield 72 of FIG. 3. The electromagnetic shield 850 includes four portions 852-858 separated by four slits 860-866. The four portions 852-858 are coupled with a conductive region 876. A bonding pad 878, allows the electromagnetic shield 850 to be coupled to a DC voltage, for example, a ground voltage.

In the presence of a magnetic field, it will be understood that eddy currents 868-874 can be induced in the electromagnetic shield 850. Due to the four slits 860-866, it will be understood that a size (i.e., a diameter or a path length) of the closed loops eddy currents 866-874 tends to be smaller than the size of the closed loop eddy currents 812, 814 of FIG. 11. It will be understood that the reduced size of the closed loops in which the eddy currents 868-874 travel results in smaller eddy currents 868-874 and a smaller local affect on the AC magnetic field that induced the eddy current than that which results from the shield 800 of FIG. 11. Therefore, the sensitivity of a magnetic field sensor on which the magnetic field sensing element 880 and the electromagnetic shield 850 are used is less affected by the smaller eddy currents 868-874 than the sensitivity of a current sensor using the shield 800 of FIG. 11.

Furthermore, by placing the shield 850 in relation to the magnetic field sensing element 880 as shown, so that the slits 860-866 pass over the magnetic field sensing element 880, it will be understood that the magnetic field associated with any one of the eddy currents 868-874, tends to form magnetic fields passing through the magnetic field sensing element 880 in two directions, canceling over at least a portion of the area of the magnetic field sensing element 880.

Referring now to FIG. 13, another exemplary electromagnetic shield 900 can be the same as or similar to the electromagnetic shield 72 of FIG. 3. The electromagnetic shield 900 includes a shielding portion 902 having interdigitated members, of which member 902a is but one example. The interdigitated members are coupled through a conductor portion 904 to a bonding pad 906, which allows the electromagnetic shield 900 to be coupled to a DC voltage, for example, a ground voltage.

It will be recognized that the electromagnetic shield 900 is able to support eddy currents having a much smaller size (i.e., diameter of path length) than the electromagnetic shield 850 of FIG. 12 or the electromagnetic shield 800 of FIG. 11. Therefore, the electromagnetic shield 900 tends to have an even smaller negative affect on sensitivity of a magnetic field sensor than that described above.

Referring now to FIG. 14, an electromagnetic shield 950 can be the same as or similar to the electromagnetic shield 72 of FIG. 3. The electromagnetic shield 950 includes a shielding portion 952 having a plurality of members, of which member 952a is but one example. The members are coupled through a conductor portion 954 to a bonding pad 956, which

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allows the electromagnetic shield **950** to be coupled to a DC voltage, for example, a ground voltage. Advantages of the electromagnetic shield **950** will be apparent from discussion above.

While shields having features to reduce eddy currents are described above, the shield **72** of FIGS. **3**, **3A**, **3C**, and **3D** can also have no features to reduce eddy currents.

Referring now to FIG. **15**, an exemplary application of the above-described magnetic field sensors includes five magnetic field sensors **1004a-1004f** arranged in a line. A gear shift lever **1000**, such as that which may be found in an automobile, can move left or right in the view shown to select a gear, which may, for example, be park (P), reverse (R), neutral (N), drive (D), second gear (2), or first gear (1). Each gear is associated with a respective one of the magnetic field sensors as shown.

The gearshift lever **1000** can have a magnet **1002** disposed on an end thereof nearest to the magnetic field sensors **1004a-1004f**. In operation, a magnetic field sensor, e.g., the magnetic field sensor **1004d**, senses when the gearshift lever **1000** is at a position of the particular magnetic field sensor, e.g., **1004d**, and thus, senses the particular gear associated with the position of the gear shift lever. In this way, the magnetic field sensors **1004a-1004f** can provide respective signals to a computer processor or the like, which can electronically/mechanically configure the automobile transmission into the selected gear.

This particular arrangement is shown to point out a potential problem with the arrangements of FIGS. **5**, **5A**, and **6**. In particular, if the magnetic field generated by the magnet **1002** is in the same direction as the magnetic field generated by the self-test conductor **224** of FIGS. **5**, **5A**, and **6**, then the magnetic field generated by the self-test conductor **224** may be overwhelmed by the magnetic field generated by the magnet, resulting in no diagnostic output signal **254a**, **254a'** (FIGS. **5**, **5A**, **6**).

In some embodiments, this shortcoming can be overcome merely by selecting the magnetic field generated by the magnet **1002** to be in a direction opposite to the direction of the magnetic field generated by the self-test conductor **224**. However, in other embodiments, it may be desirable to have a magnetic field sensor that can select and/or change a direction of the magnetic field generated by the self-test conductor **224**. An exemplary arrangement having this ability is shown in FIG. **16**.

Referring now to FIG. **16**, in which like elements of FIGS. **5**, **5A**, and **6** are shown having like reference designations, a circuit includes the self-test conductor **224**, but arranged in a different way than is shown in other figures. Though shown separately spaced in FIG. **16**, it should be understood that, like the embodiments of FIGS. **5**, **5A**, and **6**, the magnetic field sensing element **226** can be proximate to the self-test conductor **224**.

Two comparators **1010**, **1012** can be coupled to receive the signal **228a** from the amplifier **228**. The comparator **1010** can also be coupled to receive a comparison signal **1014a** representative of a signal from the amplifier **228** when the magnetic field sensing element experiences zero Gauss (or a background magnetic field, e.g., the earth's magnetic field) plus a delta. The comparator **1012** can also be coupled to receive a comparison signal **1014b** representative of a signal from the amplifier **228** when the magnetic field sensing element experiences zero Gauss (or a background magnetic field, e.g., the earth's magnetic field) minus a delta.

The comparator **1010** can generate a first comparison signal **1010a**, and the comparator **1012** can generate a second comparison signal **1012a**.

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A flip-flop (i.e., a latch) **1020** can be coupled to receive the first and second comparison signals **1010a**, **1012a**, respectively at set and reset inputs and can be configured to generate a first output signal **1020a** and a second output signal **1020b**.

A first logic gate, for example, an AND gate **1022**, can be coupled to receive the first output signal **1020a**, coupled to receive the diagnostic control signal **260a** (FIGS. **5**, **5A**, **6**), and configured to generate a control signal **1022a** (Control A).

A second logic gate, for example, an AND gate **1024**, can be coupled to receive the second output signal **1020b**, coupled to receive the diagnostic control signal **260a**, and configured to generate a control signal **1024a** (Control B).

The self-test conductor **224** can be arranged in the cross arm of an H-bridge surrounded by switches **1026a**, **1026b**, **1028a**, **1028b**. The switches **1026a**, **1026b** are controlled by the first control signal **1022a**, and the switches **1028a**, **1028b** are controlled by the second control signal **1024a**.

Thus, in operation, when the current generator **216** generates the current **218** in response to the diagnostic control signal **260a**, the current **218** flows through the self-test conductor **224** in one of two directions determined by the first and second control signals **1022a**, **1024a**.

The comparators **1010**, **1012** and the flip flop **1020** operate essentially as a window comparator, so that when the magnetic field experienced by the magnetic field sensing element **226** is large in a first direction, the diagnostic current passing through the self-test conductor **224** generates a magnetic field in an opposite second direction (when the diagnostic control signal **260a** is also high). Conversely, when the magnetic field experienced by the magnetic field sensing element **226** is large in the second direction, the diagnostic current passing through the self-test conductor **224** is in the opposite first direction (when the diagnostic control signal **260a** is also high).

With this arrangement, even in the presence of a fairly large magnetic field in either direction, which tends to saturate the magnetic field sensing element **226**, or electronics coupled to the magnetic field sensing element, for example, the amplifier **228**, still the self-test signal **218** can generate a magnetic field in the opposite direction, which can propagate to the diagnostic output signal **254**, **254a'** of FIGS. **5**, **5A**, and **6**.

It will be apparent that the circuit of FIG. **16** can be incorporated into the circuits of preceding figures.

All references cited herein are hereby incorporated herein by reference in their entirety. Having described preferred embodiments of the invention, it will now become apparent to one of ordinary skill in the art that other embodiments incorporating their concepts may be used. It is felt therefore that these embodiments should not be limited to disclosed embodiments, but rather should be limited only by the spirit and scope of the appended claims.

What is claimed is:

1. A magnetic field sensor comprising:

a magnetic field sensing element supported by a substrate, wherein the magnetic field sensing element is configured to generate a self-test signal responsive to a pulsing self-test magnetic field during one or more self-test time periods;

a self-test circuit supported by the substrate, the self-test circuit comprising:

a self test current conductor proximate to the magnetic field sensing element, the self-test current conductor for carrying a self-test current to generate the self-test magnetic field;

a processing circuit coupled to receive a signal representative of the self-test signal; and

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a diagnostic request processor configured to control the self-test current to be on or off in response to a diagnostic input signal received by the diagnostic request processor or to be indicative of a self-test during one or more time periods in response to a control signal generated by the diagnostic request processor.

2. The magnetic field sensor of claim 1, wherein the diagnostic request processor comprises a decoder coupled to receive the diagnostic input signal, configured to decode the diagnostic input signal, and configured to generate a diagnostic control signal to control the self-test current.

3. The magnetic field sensor of claim 1, wherein the diagnostic request processor comprises an internal diagnostic clock generator configured to generate the diagnostic control signal to control the self-test current to comprise a group of current pulses during the one or more time periods.

4. The magnetic field sensor of claim 1, wherein the self-test circuit further comprises:

a current generator circuit having an output node at which self-test current pulses are generated, wherein the self-test current conductor is coupled to receive the self-test current pulses resulting in the self-test magnetic field having magnetic field pulses.

5. The magnetic field sensor of claim 4, wherein the current generator is configured to generate the self-test current pulses in response to the diagnostic control signal.

6. The magnetic field sensor of claim 4, wherein the diagnostic input signal comprises control pulses, each control pulse resulting in one self-test current pulse from the current generator.

7. The magnetic field sensor of claim 4, wherein the diagnostic input signal comprises control pulses, each control pulse resulting in a plurality of self-test current pulses from the current generator.

8. The magnetic field sensor of claim 4, wherein the diagnostic input signal comprises a first state during which the current generator generates self-test current pulses and a second state during which the current generator does not generate self-test current pulses.

9. The magnetic field sensor of claim 4, wherein the diagnostic input signal comprises first control pulses with a first duty cycle during which the current generator generates self-test current pulses, and wherein the diagnostic input signal comprises second control pulses with a second duty cycle during which the current generator does not generate self-test current pulses.

10. The magnetic field sensor of claim 4 wherein the diagnostic input signal comprises a binary digital word.

11. The magnetic field sensor of claim 1, wherein the self-test current conductor comprises a conductor supported by the substrate and proximate to the magnetic field sensing element.

12. The magnetic field sensor of claim 1, wherein the self-test current conductor comprises a conductor supported by the substrate and spanning more than one metal layer supported by the substrate.

13. The magnetic field sensor of claim 1, further comprising an electromagnetic shield proximate to the magnetic field sensor.

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14. The magnetic field sensor of claim 13, wherein the electromagnetic shield comprises at least one feature configured to reduce an eddy current in the electromagnetic shield when the shield is exposed to an AC magnetic field.

15. The magnetic field sensor of claim 1, wherein the magnetic field sensing element comprises a Hall effect element, wherein the magnetic field sensor further comprises a current or voltage generator coupled to the Hall effect element.

16. The magnetic field sensor of claim 1, wherein the magnetic field sensing element comprises a magnetoresistance element, wherein the magnetic field sensor further comprises a current generator coupled to the magnetoresistance element.

17. The magnetic field sensor of claim 1, wherein the one or more self-test time periods comprises a time period beginning with a power-on of the magnetic field sensor and terminating a predetermined time thereafter.

18. A method of generating a self-test of a magnetic field sensor, comprising:

generating, with a magnetic field sensing element supported, by a substrate, a self-test signal responsive to a pulsing self-test magnetic field during one or more self-test time periods;

providing a self-test circuit supported by the substrate, the providing the self-test circuit comprising:

providing a self-test current conductor proximate to the magnetic field sensing element, the self-test current conductor for carrying a self-test current to generate the self-test magnetic field;

providing a processing circuit coupled to receive a signal representative of the self-test signal; and

providing a diagnostic request processor configured to control the self-test current to be on or off in response to a diagnostic input signal received by the diagnostic request processor or to be indicative of a self-test during one or more time periods in response to a control signal generated by the diagnostic request processor.

19. The method of claim 18, further comprising: controlling, in response to an internal control signal, the self-test current to comprise a group of current pulses during the one or more time periods.

20. The method of claim 18, wherein the self-test current conductor comprises a conductor supported by the substrate and proximate to the magnetic field sensing element.

21. The method of claim 18, wherein the self-test current conductor comprises a coil supported by the substrate and spanning more than one metal layer supported by the substrate.

22. The method of claim 21, further comprising electromagnetically shielding the magnetic field sensor.

23. The method of claim 18, further comprising electromagnetically shielding the magnetic field sensor.

24. The method of claim 18, wherein the one or more self-test time periods comprises a time period beginning with a power-on of the magnetic field sensor and terminating a predetermined time thereafter.

* * * * *

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 9,151,807 B2
APPLICATION NO. : 14/321347
DATED : October 6, 2015
INVENTOR(S) : Andreas P. Friedrich et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Specification

Column 1, line 27 delete “to a magnetic field” and replace with --to magnetic field--.

Column 3, line 19 delete “FIG. 1 is block” and replace with --FIG. 1 is a block--.

Column 3, line 39 delete “FIG. 3 is block” and replace with --FIG. 3 is a block--.

Column 3, line 45 delete “FIG. 3A is block” and replace with --FIG. 3A is a block--.

Column 3, line 49 delete “FIG. 3B is block” and replace with --FIG. 3B is a block--.

Column 3, line 53 delete “FIG. 3C is block” and replace with --FIG. 3C is a block--.

Column 3, line 59 delete “FIG. 3D is block” and replace with --FIG. 3D is a block--.

Column 4, line 41 delete “a series of graph” and replace with --a series of graphs--.

Column 6, line 16 delete “let is suffice” and replace with --let it suffice--.

Column 6, line 51 delete “that that” and replace with --that--.

Column 9, line 9 delete “conductor 30””””” and replace with --conductor 30””””--.

Column 9, line 13 delete “conductor 30””””” and replace with --conductor 30””””--.

Column 10, line 6 delete “of FIGS. 3” and replace with --of FIG. 3--.

Column 10, line 51 delete “30, 18 or FIG. 1” and replace with --30, 18 of FIG. 1--.

Signed and Sealed this
Fourteenth Day of June, 2016



Michelle K. Lee
Director of the United States Patent and Trademark Office

Specification

Column 13, line 58 delete “processor 58 or” and replace with --processor 58 of--.

Column 16, line 4 delete “pass though to” and replace with --pass through to--.

Column 22, line 26 delete “currents 866-874” and replace with --currents 868-874--.

Column 22, line 51 delete “coupled though a” and replace with --coupled through a--.

Column 22, line 67 delete “though a” and replace with --through a--.

Claims

Column 26, line 21-22 delete “element supported. by” and replace with --element supported by--.